

Automotive PSoC[®] 4: PSoC 4100 Family Datasheet

Programmable System-on-Chip (PSoC[®])

General Description

PSoC[®] 4 is a scalable and reconfigurable platform architecture for a family of mixed-signal programmable embedded system controllers with an ARM[®] Cortex [™]-M0 CPU, while being AEC-Q100 compliant. It combines programmable and re-configurable analog and digital blocks with flexible automatic routing. The PSoC 4100 product family, based on this platform, is a combination of a microcontroller with digital programmable logic, high-performance analog-to-digital conversion, opamp with Comparator mode, and standard communication and timing peripherals. The PSoC 4100 products will be fully upward compatible with members of the PSoC 4 platform for new applications and design needs. The programmable analog and digital subsystems allow flexibility and in-field tuning of the design.

Features

32-bit MCU Sub-system

- Automotive Electronics Council (AEC) AEC-Q100 qualified
- 24 MHz ARM Cortex-M0 CPU with single-cycle multiply
- Up to 32 kB of flash with Read Accelerator
- Up to 4 kB of SRAM

Programmable Analog

- One opamp with reconfigurable high-drive external and high-bandwidth internal drive, Comparator mode, and ADC input buffering capability
- 12-bit, 806 Ksps SAR ADC with differential and single-ended modes and Channel Sequencer with signal averaging
- Two current DACs (IDACs) for general-purpose or capacitive sensing applications on any pin
- Two low-power comparators that operate in Deep Sleep

Low Power 1.71 V to 5.5 V operation

- 20 nA Stop Mode with GPIO pin wakeup
- Hibernate and Deep Sleep modes allow wakeup-time versus power trade-offs

Capacitive Sensing

- Cypress Capacitive Sigma-Delta (CSD) provides best-in-class SNR (>5:1) and water tolerance
- Cypress supplied software component makes capacitive sensing design easy
- Automatic hardware tuning (SmartSense[™])

Segment LCD Drive

- LCD drive supported on all pins (common or segment)
- Operates in Deep Sleep mode with 4 bits per pin memory

Serial Communication

■ Two independent run-time reconfigurable serial communication blocks (SCBs) with reconfigurable I2C, SPI, UART, or LIN Slave 1.3, 2.1/2.2 functionality

Timing and Pulse-Width Modulation

- Four 16-bit Timer/Counter Pulse-Width Modulator (TCPWM) blocks
- Center-aligned, Edge, and Pseudo-random modes
- Comparator-based triggering of Kill signals for motor drive and other high reliability digital logic applications

Up to 24 Programmable GPIOs

- 28-pin SSOP package
- Any GPIO pin can be CapSense, LCD, analog, or digital
- Drive modes, strengths, and slew rates are programmable

Temperature Ranges:

- A Grade: –40 °C to +85 °C
- S Grade: -40 °C to +105 °C

PSoC Creator Design Environment

- Integrated Development Environment provides schematic design entry and build (with analog and digital automatic routing)
- Applications Programming Interface (API Component) for all fixed-function and programmable peripherals

Industry Standard Tool Compatibility

■ After schematic entry, development can be done with ARM-based industry-standard development tools

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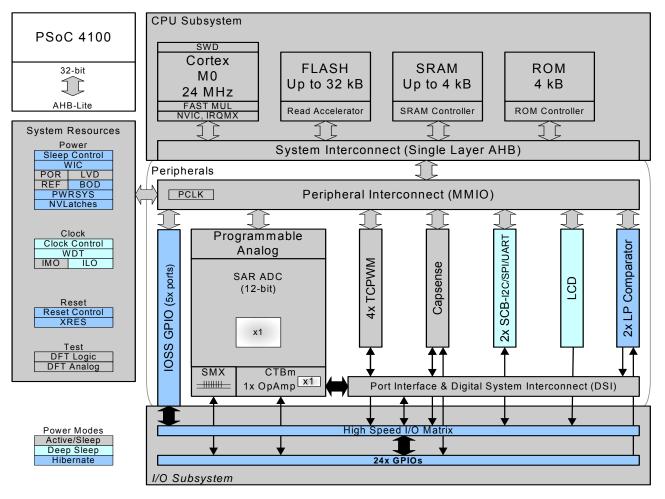
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Block Diagram



Functional Description

PSoC 4100 devices include extensive support for programming, testing, debugging, and tracing both hardware and firmware.

The ARM Serial_Wire Debug (SWD) interface supports all programming and debug features of the device.

Complete debug-on-chip functionality enables full device debugging in the final system using the standard production device. It does not require special interfaces, debugging pods, simulators, or emulators. Only the standard programming connections are required to fully support debug.

The PSoC Creator Integrated Development Environment (IDE) provides fully integrated programming and debug support for PSoC 4100 devices. The SWD interface is fully compatible with industry standard third party tools. With the ability to disable debug features, with very robust flash protection, and by allowing customer-proprietary functionality to be implemented in on-chip

programmable blocks, the PSoC 4100 family provides a level of security not possible with multi-chip application solutions or with microcontrollers.

The debug circuits are enabled by default and can only be disabled in firmware. If not enabled, the only way to re-enable them is to erase the entire device, clear flash protection, and reprogram the device with new firmware that enables debugging.

Additionally, all device interfaces can be permanently disabled (device security) for applications concerned about phishing attacks due to a maliciously reprogrammed device or attempts to defeat security by starting and interrupting flash programming sequences. Because all programming, debug, and test interfaces are disabled when maximum device security is enabled, PSoC 4100 with device security enabled may not be returned for failure analysis. This is a trade-off the PSoC 4100 allows the customer to make.



Functional Overview

CPU and Memory Subsystem

CPU

The Cortex-M0 CPU in PSoC 4100 is part of the 32-bit MCU subsystem, which is optimized for low power operation with extensive clock gating. It mostly uses 16-bit instructions and executes a subset of the Thumb-2 instruction set. This enables fully compatible binary upward migration of the code to higher performance processors such as the Cortex-M3 and M4, thus enabling upward compatibility. The Cypress implementation includes a hardware multiplier that provides a 32-bit result in one cycle. It includes a nested vectored interrupt controller (NVIC) block with 32 interrupt inputs and also includes a Wakeup Interrupt Controller (WIC), which can wake the processor up from Deep Sleep mode allowing power to be switched off to the main processor when the chip is in Deep Sleep mode. The Cortex-M0 CPU provides a Non-Maskable Interrupt input (NMI), which is made available to the user when it is not in use for system functions requested by the user.

The CPU also includes a debug interface, the Serial Wire Debug (SWD) interface, which is a 2-wire form of JTAG; the debug configuration used for PSoC 4100 has four break-point (address) comparators and two watchpoint (data) comparators.

Flash

PSoC 4100 has a flash module with a flash accelerator tightly coupled to the CPU to improve average access times from the flash block. The flash block is designed to deliver 0 wait-state (WS) access time at 24 MHz. Part of the flash module can be used to emulate EEPROM operation if required.

The PSoC 4100 flash supports the following flash protection modes at the memory sub-system level.

Open: No protection. Factory default mode that the product is shipped in.

Protected: User may change from Open to Protected. This mode disables debug interface accesses. The mode can be set back to Open but only after completely erasing the flash.

Kill: User may change from Open to Kill. This mode disables all debug accesses. The part cannot be erased externally, thus obviating the possibility of partial erasure by power interruption and potential malfunction and security leaks. This is an irrecvocable mode.

In addition, row-level Read/Write protection is also supported to prevent inadvertent Writes as well as selectively block Reads. Flash Read/Write/Erase operations are always available for internal code using system calls.

SRAM

SRAM memory is retained during Hibernate.

SROM

A supervisory ROM that contains boot and configuration routines is provided.

System Resources

Power System

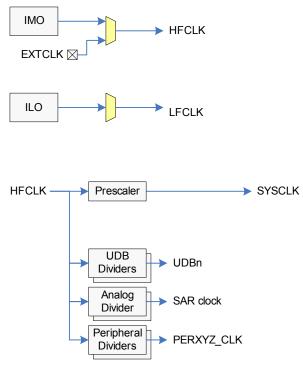
The power system is described in detail in the section Power on page 10. It provides assurance that voltage levels are as required for each respective mode and either delay mode entry (on power-on reset (POR), for example) until voltage levels are as required for proper function or generate resets (brown-out detect (BOD)) or interrupts (low-voltage detect (LVD)). The PSoC 4100 operates with a single external supply over the range of 1.71 V to 5.5 V and has five different power modes, transitions between which are managed by the power system. The PSoC 4100 provides Sleep, Deep Sleep, Hibernate, and Stop low-power modes.

Clock System

The PSoC 4100 clock system is responsible for providing clocks to all subsystems that require clocks and for switching between different clock sources without glitching. In addition, the clock system ensures that no metastable conditions occur.

The clock system for the PSoC 4100 consists of two internal oscillators, IMO and the ILO, and provision for an external clock.

Figure 1. PSoC 4100 MCU Clocking Architecture



The HFCLK signal can be divided down (see PSoC 4100 MCU Clocking Architecture) to generate synchronous clocks for the analog and digital peripherals. There are a total of 12 clock dividers for the PSoC 4100, each with 16-bit divide capability. The analog clock leads the digital clocks to allow analog events to occur before digital clock-related noise is generated. The 16-bit capability allows a lot of flexibility in generating fine-grained frequency values and is fully supported in PSoC Creator.



IMO Clock Source

The IMO is the primary source of internal clocking in the PSoC 4100. It is trimmed during testing to achieve the specified accuracy. Trim values are stored in nonvolatile latches (NVL). Additional trim settings from flash can be used to compensate for changes. The IMO default frequency is 24 MHz and it can be adjusted between 3 MHz to 24 MHz in steps of 1 MHz. IMO tolerance with Cypress-provided calibration settings is $\pm 2\%$.

ILO Clock Source

The ILO is a very low power oscillator, which is primarily used to generate clocks for peripheral operation in Deep Sleep mode. ILO-driven counters can be calibrated to the IMO to improve accuracy. Cypress provides a software component, which does the calibration.

Watchdog Timer

A watchdog timer is implemented in the clock block running from the ILO; this allows watchdog operation during Deep Sleep and generates a watchdog reset if not serviced before the timeout occurs. The watchdog reset is recorded in the Reset Cause register.

Reset

PSoC 4100 can be reset from a variety of sources including a software reset. Reset events are asynchronous and guarantee reversion to a known state. The reset cause is recorded in a register, which is sticky through reset and allows software to determine the cause of the Reset. An XRES pin is reserved for external reset to avoid complications with configuration and multiple pin functions during power-on or reconfiguration. The XRES pin has an internal pull-up resistor that is always enabled.

Voltage Reference

The PSoC 4100 reference system generates all internally required references. A 1% voltage reference spec is provided for the 12-bit ADC. To allow better signal-to-noise ratios (SNR) and better absolute accuracy, it is possible to bypass the internal reference using a GPIO pin or to use an external reference for the SAR.

Analog Blocks

12-bit SAR ADC

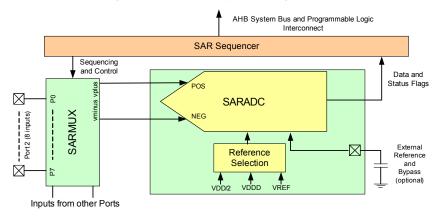
The 12-bit 806 Ksps SAR ADC can operate at a maximum clock rate of 14.5 MHz and requires a minimum of 18 clocks at that frequency to do a 12-bit conversion.

The block functionality is augmented for the user by adding a reference buffer to it (trimmable to $\pm 1\%$) and by providing the choice (for the PSoC 4100 case) of three internal voltage references: V_{DD}, V_{DD}/2, and V_{REF} (nominally 1.024 V) as well as an external reference through a GPIO pin. The Sample-and-Hold (S/H) aperture is programmable allowing the gain bandwidth requirements of the amplifier driving the SAR inputs, which determine its settling time, to be relaxed if required. System performance will be 65 dB for true 12-bit precision providing appropriate references are used and system noise levels permit. To improve performance in noisy conditions, it is possible to provide an external bypass (through a fixed pin location) for the internal reference amplifier.

The SAR is connected to a fixed set of pins through an 8-input sequencer. The sequencer cycles through selected channels autonomously (sequencer scan) and does so with zero switching overhead (that is, aggregate sampling bandwidth is equal to 806 Ksps whether it is for a single channel or distributed over several channels). The sequencer switching is effected through a state machine or through firmware-driven switching. A feature provided by the sequencer is buffering of each channel to reduce CPU interrupt service requirements. To accommodate signals with varying source impedance and frequency, it is possible to have different sample times programmable for each channel. Also, signal range specification through a pair of range registers (low and high range values) is implemented with a corresponding out-of-range interrupt if the digitized value exceeds the programmed range; this allows fast detection of out-of-range values without the necessity of having to wait for a sequencer scan to be completed and the CPU to read the values and check for out-of-range values in software.

The SAR is able to digitize the output of the on-board temperature sensor for calibration and other temperature-dependent functions. The SAR is not available in Deep Sleep and Hibernate modes as it requires a high-speed clock (up to 18 MHz). The SAR operating range is 1.71 V to 5.5 V.

Figure 2. SAR ADC System Diagram





Opamp (CTBm Block)

PSoC 4100 has an opamp with Comparator mode, which allows most common analog functions to be performed on-chip eliminating external components; PGAs, voltage buffers, filters, trans-impedance amplifiers, and other functions can be realized with external passives saving power, cost, and space. The on-chip opamp is designed with enough bandwidth to drive the S/H circuit of the ADC without requiring external buffering.

Temperature Sensor

PSoC 4100 has one on-chip temperature sensor This consists of a diode, which is biased by a current source that can be disabled to save power. The temperature sensor is connected to the ADC, which digitizes the reading and produces a temperature value using Cypress supplied software that includes calibration and linearization.

Low-power Comparators

PSoC 4100 has a pair of low-power comparators, which can also operate in the Deep Sleep and Hibernate modes. This allows the analog system blocks to be disabled while retaining the ability to monitor external voltage levels during low-power modes. The comparator outputs are normally synchronized to avoid metastability unless operating in an asynchronous power mode (Hibernate) where the system wake-up circuit is activated by a comparator switch event.

Fixed Function Digital

Timer/Counter/PWM Block

The Timer/Counter/PWM block consists of four 16-bit counters with user-programmable period length. There is a Capture register to record the count value at the time of an event (which may be an I/O event), a period register which is used to either stop or auto-reload the counter when its count is equal to the period register, and compare registers to generate compare value signals which are used as PWM duty cycle outputs. The block also provides true and complementary outputs with programmable offset between them to allow use as deadband programmable complementary PWM outputs. It also has a Kill input to force outputs to a predetermined state; for example, this is used in motor drive systems when an overcurrent state is indicated and the PWMs driving the FETs need to be shut off immediately with no time for software intervention.

Serial Communication Blocks (SCB)

PSoC 4100 has two SCBs, which can each implement an I^2C , UART, SPI, or LIN Slave interface.

I²C Mode: The hardware I²C block implements a full multi-master and slave interface (it is capable of multimaster arbitration). This block is capable of operating at speeds of up to 1 Mbps (Fast Mode Plus) and has flexible buffering options to reduce interrupt overhead and latency for the CPU. The FIFO mode is available in all channels and is very useful in the absence of DMA.

The I^2C peripheral is compatible with the I^2C Standard-mode, Fast-mode, and Fast-mode Plus devices as defined in the NXP I^2C -bus specification and user manual (UM10204). The I^2C bus I/O is implemented with GPIO in open-drain modes. The I2C bus uses open-drain drivers for clock and data with pull-up resistors on the bus for clock and data connected to all nodes. Required Rise and Fall times for different I2C speeds are guaranteed by using appropriate pull-up resistor values depending on V_{DD} , Bus Capacitance, and resistor tolerance. For detailed information on how to calculate the optimum pull-up resistor value for your design, please refer to the UM10204 I²C bus specification and user manual, the newest revision is available at www.nxp.com.

The PSoC 4100 is not completely compliant with the I^2C spec in the following respects:

- GPIO cells are not overvoltage tolerant and, therefore, cannot be hot-swapped or powered up independently of the rest of the I²C system.
- Fast-mode Plus has an I_{OL} specification of 20 mA at a V_{OL} of 0.4 V. The GPIO cells can sink a maximum of 8 mA I_{OL} with a V_{OL} maximum of 0.6 V.
- Fast-mode and Fast-mode Plus specify minimum Fall times, which are not met with the GPIO cell; Slow strong mode can help meet this spec depending on the Bus Load.
- When the SCB is an I²C Master, it interposes an IDLE state between NACK and Repeated Start; the I²C spec defines Bus free as following a Stop condition so other Active Masters do not intervene but a Master that has just become activated may start an Arbitration cycle.
- When the SCB is in I²C Slave mode, and Address Match on External Clock is enabled (EC_AM = 1) along with operation in the internally clocked mode (EC_OP = 0), then its I²C address must be even.

UART Mode: This is a full-feature UART operating at up to 1 Mbps. It supports automotive single-wire interface (LIN), infrared interface (IrDA), and SmartCard (ISO7816) protocols, all of which are minor variants of the basic UART protocol. In addition, it supports the 9-bit multiprocessor mode that allows addressing of peripherals connected over common RX and TX lines. Common UART functions such as parity error, break detect, and frame error are supported. An 8-deep FIFO allows much greater CPU service latencies to be tolerated.

SPI Mode: The SPI mode supports full Motorola SPI, TI SSP (essentially adds a start pulse used to synchronize SPI Codecs), and National Microwire (half-duplex form of SPI). The SPI block can use the FIFO and also supports an EzSPI mode in which data interchange is reduced to reading and writing an array in memory.

LIN Slave Mode: The LIN Slave mode uses the SCB hardware block and implements a full LIN slave interface. This LIN slave is compliant with LIN v1.3 and LIN v2.1/2.2 specification standards. It is certified by C&S GmbH based on the standard protocol and data link layer conformance tests. The LIN slave can be operated at baud rates of up to ~20 Kbps with a maximum of 40-meter cable length. PSoC Creator software supports up to two LIN slave interfaces in the PSoC 4 device, providing built-in application programming interfaces (APIs) based on the LIN specification standard.





GPIO

PSoC 4100 has 24 GPIOs. The GPIO block implements the following:

- Eight drive strength modes:
 - □ Analog input mode (input and output buffers disabled)
 - □ Input only
 - Weak pull-up with strong pull-down
 - □ Strong pull-up with weak pull-down
 - Open drain with strong pull-down
 - Open drain with strong pull-up
 - Strong pull-up with strong pull-down
 - Weak pull-up with weak pull-down
- Input threshold select (CMOS or LVTTL).
- Individual control of input and output buffer enabling/disabling in addition to the drive strength modes.
- Hold mode for latching previous state (used for retaining I/O state in Deep Sleep mode and Hibernate modes).
- Selectable slew rates for dV/dt related noise control to improve EMI.

The pins are organized in logical entities called ports, which are 8-bit in width. During power-on and reset, the blocks are forced to the disable state so as not to crowbar any inputs and/or cause excess turn-on current. A multiplexing network known as a high-speed I/O matrix is used to multiplex between various signals that may connect to an I/O pin. Pin locations for fixed-function peripherals are also fixed to reduce internal multiplexing complexity.

Data output and pin state registers store, respectively, the values to be driven on the pins and the states of the pins themselves.

Every I/O pin can generate an interrupt if so enabled and each I/O port has an interrupt request (IRQ) and interrupt service routine (ISR) vector associated with it (5 for PSoC 4100).

Special Function Peripherals

LCD Segment Drive

The PSoC 4100 has an LCD controller which can drive up to four commons and up to 32 segments. It uses full digital methods to drive the LCD segments requiring no generation of internal LCD voltages. The two methods used are referred to as digital correlation and PWM.

Digital correlation pertains to modulating the frequency and levels of the common and segment signals to generate the highest RMS voltage across a segment to light it up or to keep the RMS signal zero. This method is good for STN displays but may result in reduced contrast with TN (cheaper) displays.

PWM pertains to driving the panel with PWM signals to effectively use the capacitance of the panel to provide the integration of the modulated pulse-width to generate the desired LCD voltage. This method results in higher power consumption but can result in better results when driving TN displays. LCD operation is supported during Deep Sleep refreshing a small display buffer (4 bits; 1 32-bit register per port).

CapSense

CapSense is supported on all pins in the PSoC 4100 through a CapSense Sigma-Delta (CSD) block that can be connected to any pin through an analog mux bus that any GPIO pin can be connected to via an Analog switch. CapSense function can thus be provided on any pin or group of pins in a system under software control. A component is provided for the CapSense block to make it easy for the user.

Shield voltage can be driven on another Mux Bus to provide water tolerance capability. Water tolerance is provided by driving the shield electrode in phase with the sense electrode to keep the shield capacitance from attenuating the sensed input.

The CapSense block has two IDACs which can be used for general purposes if CapSense is not being used. (both IDACs are available in that case) or if CapSense is used without water tolerance (one IDAC is available).



Pinouts

The following is the pin-list for PSoC 4100. Port 2 comprises of the high-speed Analog inputs for the SAR Mux. P1.7 is the optional external input and bypass for the SAR reference. Ports 3 and 4 contain the Digital Communication channels. All pins support CSD CapSense and Analog Mux Bus connections.

Pi	Pins 28-SSOP Alternate Functions for Pins								Die Deserintien
Name	Туре	Pin	Name	Analog	Alt 1	Alt 2	Alt 3	Alt 4	Pin Description
VSSD	Power	DN	-	-	-	-	-	-	Digital Ground
P2.2	GPIO	5	P2.2	sarmux.2	-	-	-	-	Port 2 Pin 2: gpio, lcd, csd, sarmux
P2.3	GPIO	6	P2.3	sarmux.3	-	-	-	-	Port 2 Pin 3: gpio, lcd, csd, sarmux
P2.4	GPIO	7	P2.4	sarmux.4	tcpwm0_p[1]	_	_	-	Port 2 Pin 4: gpio, lcd, csd, sarmux, pwm
P2.5	GPIO	8	P2.5	sarmux.5	tcpwm0_n[1]	-	_	-	Port 2 Pin 5: gpio, lcd, csd, sarmux, pwm
P2.6	GPIO	9	P2.6	sarmux.6	tcpwm1_p[1]	_	_	-	Port 2 Pin 6: gpio, lcd, csd, sarmux, pwm
P2.7	GPIO	10	P2.7	sarmux.7	tcpwm1_n[1]	_	_	-	Port 2 Pin 7: gpio, lcd, csd, sarmux, pwm
P3.0	GPIO	11	P3.0	-	tcpwm0_p[0]	scb1_uart_rx[0]	scb1_i2c_scl[0]	scb1_spi_mosi[0]	Port 3 Pin 0: gpio, lcd, csd, pwm, scb1
P3.1	GPIO	12	P3.1	-	tcpwm0_n[0]	scb1_uart_tx[0]	scb1_i2c_sda[0]	scb1_spi_miso[0]	Port 3 Pin 1: gpio, lcd, csd, pwm, scb1
P3.2	GPIO	13	P3.2	-	tcpwm1_p[0]	-	swd_io	scb1_spi_clk[0]	Port 3 Pin 2: gpio, lcd, csd, pwm, scb1, swd
P3.3	GPIO	14	P3.3	-	tcpwm1_n[0]	-	swd_clk	scb1_spi_ssel_0[0]	Port 3 Pin 3: gpio, lcd, csd, pwm, scb1, swd
P4.0	GPIO	15	P4.0	-	_	scb0_uart_rx	scb0_i2c_scl	scb0_spi_mosi	Port 4 Pin 0: gpio, lcd, csd, scb0
P4.1	GPIO	16	P4.1	-	-	scb0_uart_tx	scb0_i2c_sda	scb0_spi_miso	Port 4 Pin 1: gpio, lcd, csd, scb0
P4.2	GPIO	17	P4.2	csd_c_mod	-	-	-	scb0_spi_clk	Port 4 Pin 2: gpio, lcd, csd, scb0
P4.3	GPIO	18	P4.3	csd_c_sh_tan k	-	-	-	scb0_spi_ssel_0	Port 4 Pin 3: gpio, lcd, csd, scb0
P0.0	GPIO	19	P0.0	comp1_inp	-	-	-	scb0_spi_ssel_1	Port 0 Pin 0: gpio, lcd, csd, scb0, comp
P0.1	GPIO	20	P0.1	comp1_inn	-	-	-	scb0_spi_ssel_2	Port 0 Pin 1: gpio, lcd, csd, scb0, comp
P0.2	GPIO	21	P0.2	comp2_inp	-	-	-	scb0_spi_ssel_3	Port 0 Pin 2: gpio, lcd, csd, scb0, comp
P0.3	GPIO	22	P0.3	comp2_inn	-	-	-	-	Port 0 Pin 3: gpio, lcd, csd, comp
P0.6	GPIO	23	P0.6	-	ext_clk	-	-	scb1_spi_clk[1]	Port 0 Pin 6: gpio, lcd, csd, scb1, ext_clk
P0.7	GPIO	24	P0.7	-	-	-	wakeup	scb1_spi_ssel_0[1]	Port 0 Pin 7: gpio, lcd, csd, scb1, wakeup
XRES	XRES	25	XRES	-	-	-	-	-	Chip reset, active low
VCCD	Power	26	VCCD	-	-	-	_	-	Regulated supply, connect to 1 μF cap or 1.8 V
VDDD	Power	27	VDDD	-	-	-	-	-	Common power supply (Analog & Digital) 1.8 V–5.5 V
VSSA	Power	28(DN)	VSS	-	-	-	_	-	Analog Ground
P1.0	GPIO	1	P1.0	ctb.oa0.inp	tcpwm2_p[1]	-	-	-	Port 1 Pin 0: gpio, lcd, csd, ctb, pwm
P1.1	GPIO	2	P1.1	ctb.oa0.inm	tcpwm2_n[1]	-	-	-	Port 1 Pin 1: gpio, lcd, csd, ctb, pwm
P1.2	GPIO	3	P1.2	ctb.oa0.out	tcpwm3_p[1]	-	-	-	Port 1 Pin 2: gpio, lcd, csd, ctb, pwm
P1.7	GPIO	4	P1.7	ctb.oa1.inp_a It ext_vref	-	-	-	-	Port 1 Pin 7: gpio, lcd, csd, ext_ref

Notes:

1. tcpwm_p and tcpwm_n refer to tcpwm non-inverted and inverted outputs respectively.

2. P3.2 and P3.3 are SWD pins after boot (reset).

Descriptions of the pin functions are as follows:

VDDD: Power supply for both analog and digital sections (where there is no V_{DDA} pin).



VDDA: Analog V_{DD} pin where package pins allow; shorted to V_{DDD} otherwise.

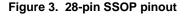
VSSA: Analog ground pin where package pins allow; shorted to VSS otherwise

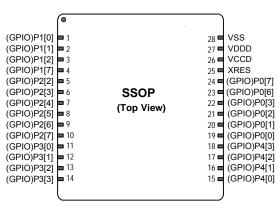
VSS: Ground pin.

VCCD: Regulated Digital supply (1.8 V ±5%).

Port Pins can all be used as LCD Commons, LCD Segment drivers, or CSD sense and shield pins can be connected to AMUXBUS A or B or can all be used as GPIO pins that can be driven by firmware or DSI signals.

The following package is supported: 28-pin SSOP.



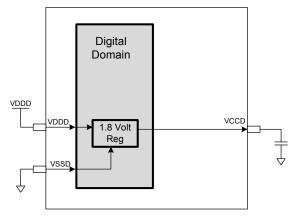




Power

The following power system diagram shows the minimum set of power supply pins as implemented for the PSoC 4100. The system has one regulator in Active mode for the digital circuitry. There is no analog regulator; the analog circuits run directly from the V_{DDA} input. There are separate regulators for the Deep Sleep and Hibernate (lowered power supply and retention) modes. There is a separate low-noise regulator for the bandgap. The supply voltage range is 1.71 to 5.5 V with all functions and circuits operating over that range.

Figure 4. PSoC 4 Power Supply



The PSoC 4100 family allows two distinct modes of power supply operation: Unregulated External Supply, and Regulated External Supply modes.

Unregulated External Supply

In this mode, PSoC 4100 is powered by an External Power Supply that can be anywhere in the range of 1.8 V to 5.5 V. This range is also designed for battery-powered operation, for instance, the chip can be powered from a battery system that starts at 3.5 V and works down to 1.8 V. In this mode, the internal regulator of the PSoC 4100 supplies the internal logic and the VCCD output of the PSoC 4100 must be bypassed to ground via an external Capacitor (in the range of 1 to 1.6 μ F; X5R ceramic or better).

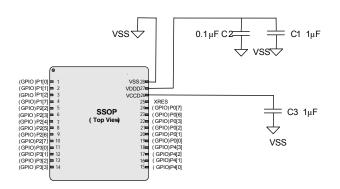
Bypass capacitors must be used from VDDD to ground, typical practice for systems in this frequency range is to use a capacitor in the 1- μ F range in parallel with a smaller capacitor (0.1 μ F for example). Note that these are simply rules of thumb and that, for critical applications, the PCB layout, lead inductance, and the Bypass capacitor parasitic should be simulated to design and obtain optimal bypassing.

An example of a bypass scheme for the 28-pin SSOP package follows.

Table 1. Example of a bypass scheme

Power Supply	Bypass Capacitors
VDDD-VSS	0.1 μ F ceramic capacitor (C2) plus bulk capacitor 1 to 10 μ F (C1). Total Capacitance may be greater than 10 μ F.
VCCD-VSS	1 μ F ceramic capacitor at the VCCD pin (C3)
VREF–VSS (optional)	The internal bandgap may be bypassed with a 1 μ F to 10 μ F capacitor. Total capacitance may be greater than 10 μ F.

Figure 5. 28-Pin SSOP Example



Regulated External Supply

In this mode, the PSoC 4100 is powered by an external power supply that must be within the range of 1.71 to $1.89 \text{ V} (1.8 \pm 5\%)$; note that this range needs to include power supply ripple too. In this mode, VCCD, and VDDD pins are all shorted together and bypassed. The internal regulator is disabled in firmware.



Development Support

The PSoC 4100 family has a rich set of documentation, development tools, and online resources to assist you during your development process. Visit www.cypress.com/go/psoc4 to find out more.

Documentation

A suite of documentation supports the PSoC 4100 family to ensure that you can find answers to your questions quickly. This section contains a list of some of the key documents.

Software User Guide: A step-by-step guide for using PSoC Creator. The software user guide shows you how the PSoC Creator build process works in detail, how to use source control with PSoC Creator, and much more.

Component Datasheets: The flexibility of PSoC allows the creation of new peripherals (components) long after the device has gone into production. Component data sheets provide all of the information needed to select and use a particular component, including a functional description, API documentation, example code, and AC/DC specifications.

Application Notes: PSoC application notes discuss a particular application of PSoC in depth; examples include brushless DC motor control and on-chip filtering. Application notes often include example projects in addition to the application note document.

Technical Reference Manual: The Technical Reference Manual (TRM) contains all the technical detail you need to use a PSoC device, including a complete description of all PSoC registers. The TRM is available in the Documentation section at www.cypress.com/psoc4.

Online

In addition to print documentation, the Cypress PSoC forums connect you with fellow PSoC users and experts in PSoC from around the world, 24 hours a day, 7 days a week.

Tools

With industry standard cores, programming, and debugging interfaces, the PSoC 4100 family is part of a development tool ecosystem. Visit us at www.cypress.com/go/psoccreator for the latest information on the revolutionary, easy to use PSoC Creator IDE, supported third party compilers, programmers, debuggers, and development kits.



Electrical Specifications

Absolute Maximum Ratings

Table 2. Absolute Maximum Ratings^[1]

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/ Conditions
SID1	V _{DDD_ABS}	Digital supply relative to V _{SSD}	-0.5	-	6	V	Absolute max
SID2	V _{CCD_ABS}	Direct digital core voltage input relative to V_{SSD}	-0.5	-	1.95	V	Absolute max
SID3	V _{GPIO_ABS}	GPIO voltage	-0.5	-	V _{DD} +0.5	V	Absolute max
SID4	I _{GPIO_ABS}	Maximum current per GPIO	-25	-	25	mA	Absolute max
SID5	I _{GPIO_injection}	GPIO injection current, Max for V _{IH} > V _{DDD} , and Min for V _{IL} < V _{SS}	-0.5	-	0.5	mA	Absolute max, current injected per pin
BID44	ESD_HBM	Electrostatic discharge human body model	2200	-	-	V	
BID45	ESD_CDM	Electrostatic discharge charged device model	500	-	_	V	
BID46	LU	Pin current for latch-up	-200	-	200	mA	

Note
 Usage above the absolute maximum conditions listed in Table 2 may cause permanent damage to the device. Exposure to absolute maximum conditions for extended periods of time may affect device reliability. The maximum storage temperature is 150 °C in compliance with JEDEC Standard JESD22-A103, High Temperature Storage Life. When used below absolute maximum conditions but above normal operating conditions, the device may not operate to specification.



Device-Level Specifications

All specifications are valid for –40 °C \leq T_A \leq 85 °C for A grade devices and -40 °C \leq T_A \leq 105 °C for S grade devices, except where noted. Specifications are valid for 1.71 V to 5.5 V, except where noted.

Table 3. DC Specifications

DB $(V_{DDA} = V_{DD})^{\circ}$ Image: constraint of the section of the sectin of the section of the section of the section of the s	Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID54V _{CCD} Output voltage (for core logic)-1.8-VSID55C _{EFC} External regulator voltage bypass11.31.6 μ FXSR ceramic or betterSID56C _{EXC} Power supply decoupling capacitor-1- μ FXSR ceramic or betterActive Mode, V _{DD} = 1.71 V to 5.5 V. Typical Values measured at V _{DD} = 3.3 V.SID9I _{D04} Execute from Flash; CPU at 6 MHz2.8mASID10I _{DD5} Execute from Flash; CPU at 6 MHz4.2mASID112IbD7Execute from Flash; CPU at 12 MHz4.2mASID13IbD8Execute from Flash; CPU at 12 MHz3.7-mAT = 25 °CSID16I _{DD11} Execute from Flash; CPU at 24 MHz-6.7-mAT = 25 °CSID16I _{DD11} Execute from Flash; CPU at 24 MHz7.2mASID25I _{DD20} I ² C wakeup, WDT, and Comparators on. 6 MHz1.31.8mAV _{DD} = 1.71 V to 5.5 VSID25I _{DD20} I ² C wakeup and WDT on. and Comparators on. 12 MHz1.3- μ AT = 25 °CSID31I _{DD26} I ² C wakeup and WDT on. and Comparators on. 12 MHz1.31.8mAV _{DD} = 1.71 V to 5.5 VSID32I _{DD27} I ² C wakeup and WDT on. and Comparators on. 12 MHz1.3- μ AT = 25 °CSID34 <td>SID53</td> <td>V_{DD}</td> <td></td> <td>1.8</td> <td>-</td> <td>5.5</td> <td>V</td> <td>With regulator enabled</td>	SID53	V _{DD}		1.8	-	5.5	V	With regulator enabled
CouldCouldCould of the probability	SID255	V _{DDD}	Power supply input voltage unregulated	1.71	1.8	1.89	V	
SID56 C_{Exc} Power supply decoupling capacitor - 1 - μ F X5R ceramic or better Active Mode, $V_{DD} = 1.71$ V to 5.5 V. Typical Values measured at $V_{DD} = 3.3$ V. SID9 I_{DD4} Execute from Flash; CPU at 6 MHz - - - 2.8 mA SID10 I_{DD5} Execute from Flash; CPU at 6 MHz - - 2.2 - mA T = 25 °C SID12 I_{DD7} Execute from Flash; CPU at 12 MHz - - 4.2 mA T = 25 °C SID13 I_{DD6} Execute from Flash; CPU at 12 MHz - 3.7 - mA T = 25 °C SID16 I_{DD11} Execute from Flash; CPU at 24 MHz - 6.7 - mA T = 25 °C SID17 I_{DD12} Execute from Flash; CPU at 24 MHz - 1.3 1.8 mA $V_{DD} = 1.71 V to 5.5 V SID25 I_{D200} I^2 C wakeup, WDT,and Comparators on. 6 MHz. - 1.3 1.8 mA V_{DD} = 1.71 V to 5.5 V SID25 I_{D200} I^2 C wakeup and WDT on. - 1.3 1.8 mA $	SID54	V _{CCD}	Output voltage (for core logic)	_	1.8	-	V	
Active Mode, $V_{DD} = 1.71$ V to 5.5 V. Typical Values measured at $V_{DD} = 3.3$ V. SID9 I _{DD4} Execute from Flash; CPU at 6 MHz - - 2.8 mA SID10 I _{DD5} Execute from Flash; CPU at 6 MHz - - 2.2 - mA T = 25 °C SID12 I _{DD7} Execute from Flash; CPU at 12 MHz - - 4.2 mA T = 25 °C SID13 I _{DD8} Execute from Flash; CPU at 12 MHz - - 3.7 - mA T = 25 °C SID16 I _{DD11} Execute from Flash; CPU at 24 MHz - 6.7 - mA T = 25 °C SID17 I _{DD12} Execute from Flash; CPU at 24 MHz - 1.3 1.8 mA V _{DD} = 1.71 V to 5.5 V SID25 I _{DD20} I ² C wakeup, WDT, and Comparators on .6 MHz. - 1.3 1.8 mA V _{DD} = 1.71 V to 5.5 V SID25 I _{DD20} I ² C wakeup and WDT on. - 1.3 1.8 mA V _{DD} = 1.71 V to 5.5 V SID25 I _{DD20} I ² C wakeup and WDT on. - 1.3 - 4A T = 25 °C <td>SID55</td> <td>C_{EFC}</td> <td>External regulator voltage bypass</td> <td>1</td> <td>1.3</td> <td>1.6</td> <td>μF</td> <td>X5R ceramic or better</td>	SID55	C _{EFC}	External regulator voltage bypass	1	1.3	1.6	μF	X5R ceramic or better
SID9 ID04 Execute from Flash; CPU at 6 MHz - - - - 2.8 mA SID10 IDD5 Execute from Flash; CPU at 6 MHz - - 2.2 - mA T = 25 °C SID12 IDD7 Execute from Flash; CPU at 12 MHz - - 4.2 mA SID13 IDD8 Execute from Flash; CPU at 12 MHz - 3.7 - mA T = 25 °C SID16 IDD11 Execute from Flash; CPU at 24 MHz - 6.7 - mA T = 25 °C SID17 IDD12 Execute from Flash; CPU at 24 MHz - 6.7 - mA T = 25 °C SID17 IDD12 Execute from Flash; CPU at 24 MHz - 1.3 1.8 mA VDD 1.71 V to 5.5 V SID25 IDD20 I ² C wakeup, WDT, and Comparators on. 6 MHz. - 1.3 1.8 mA VDD = 1.71 V to 5.5 V SID25 IDD20 I ² C wakeup and WDT on. - 1.7 2.2 mA T = 25 °C	SID56	C _{EXC}	Power supply decoupling capacitor	-	1	-	μF	X5R ceramic or better
Image: CPU at 6 MHz CPU at 6 MHz MA T Signed Stress CPU at 6 MHz MA T = 25 °C SID10 Ipp5 Execute from Flash; CPU at 12 MHz - - 4.2 mA T = 25 °C SID13 Ipp6 Execute from Flash; CPU at 12 MHz - - 3.7 - mA T = 25 °C SID16 Ipp1 Execute from Flash; CPU at 24 MHz - 6.7 - mA T = 25 °C SID17 Ipp12 Execute from Flash; CPU at 24 MHz - 6.7 - mA T = 25 °C SID17 Ipp12 Execute from Flash; CPU at 24 MHz - 6.7 - mA T = 25 °C SID17 Ipp12 Execute from Flash; CPU at 24 MHz - - 7.2 mA T SID25 Ipp12 Execute from Flash; CPU at 24 MHz - 1.3 1.8 mA Vpp = 1.71 V to 5.5 V SID25 Ipp20 I ² C wakeup, WDT, and Comparators on. 12 MHz. - 1.7 2.2 mA Vpp = 1.71 V to 5.5 V </td <td>Active Mode</td> <td>, V_{DD} = 1.71 V to</td> <td>5.5 V. Typical Values measured at V_{DD}</td> <td>= 3.3</td> <td>V.</td> <td></td> <td></td> <td></td>	Active Mode	, V _{DD} = 1.71 V to	5.5 V. Typical Values measured at V_{DD}	= 3.3	V.			
BDS CPU at 6 MHz - - 4.2 mA SID12 IDD7 Execute from Flash; CPU at 12 MHz - - 4.2 mA SID13 IDD8 Execute from Flash; CPU at 12 MHz - 3.7 - mA T = 25 °C SID16 IDD11 Execute from Flash; CPU at 24 MHz - 6.7 - mA T = 25 °C SID17 IDD12 Execute from Flash; CPU at 24 MHz - 6.7 - mA T = 25 °C SID17 IDD12 Execute from Flash; CPU at 24 MHz - 1.3 1.8 mA V_DD = 1.71 V to 5.5 V SID25 IDD20 I ² C wakeup, WDT, and Comparators on. 6 MHz. - 1.3 1.8 mA V_DD = 1.71 V to 5.5 V SID25 IDD20A I ² C wakeup, WDT, and Comparators on. 12 MHz. - 1.7 2.2 mA V_DD = 1.71 V to 5.5 V SID25 IDD20A I ² C wakeup and WDT on. - 1.3 - μA T = 25 °C SID31 IDD26 I ² C wakeup and WDT on. - 1.5 15 μA T = 25 °C	SID9	I _{DD4}		-	_	2.8	mA	
CPU at 12 MHz mA T = 25 °C SID13 I_{DD8} Execute from Flash; CPU at 12 MHz - 3.7 - mA T = 25 °C SID16 I_{DD11} Execute from Flash; CPU at 24 MHz - 6.7 - mA T = 25 °C SID17 I_{DD12} Execute from Flash; CPU at 24 MHz - - 6.7 - mA T = 25 °C SID17 I_{DD12} Execute from Flash; CPU at 24 MHz - - 7.2 mA T SID25 I_{DD20} I²C wakeup, WDT, and Comparators on. 6 MHz. - 1.3 1.8 mA V_{DD} = 1.71 V to 5.5 V SID25A I_{DD20} I²C wakeup, WDT, and Comparators on. 12 MHz. - 1.7 2.2 mA V_{DD} = 1.71 V to 5.5 V SID31 I_{DD26} I²C wakeup and WDT on. - 1.3 - μA T = 25 °C SID32 I_{DD27} I²C wakeup and WDT on. - 1.3 - μA T = 25 °C SID34 I_{DD29} I²C wakeup and WDT on. - 1.5 15 μA T = 25 °C <td>SID10</td> <td>I_{DD5}</td> <td></td> <td>-</td> <td>2.2</td> <td>-</td> <td>mA</td> <td>T = 25 °C</td>	SID10	I _{DD5}		-	2.2	-	mA	T = 25 °C
Loo CPU at 12 MHz Image: CPU at 24 MHz Image: CPU at 25 mt Image: CPU at 24 MHz Image: CPU at 24 MHz Image: CPU at 24 MHz Image: CPU at 25 mt Image: CPU at 25 mt <	SID12	I _{DD7}		-	_	4.2	mA	
DD11 CPU at 24 MHz Image: constraint of the strength of the strengt of the strength of the strength of the stren	SID13	I _{DD8}		-	3.7	-	mA	T = 25 °C
DD12 CPU at 24 MHz Image: constraint of the system of th	SID16	I _{DD11}		-	6.7	-	mA	T = 25 °C
SID25 IDD20 I ² C wakeup, WDT, and Comparators on. 6 MHz. - 1.3 1.8 mA $V_{DD} = 1.71 V \text{ to } 5.5 V$ SID25A IDD20A I ² C wakeup, WDT, and Comparators on. 12 MHz. - 1.7 2.2 mA $V_{DD} = 1.71 V \text{ to } 5.5 V$ Deep Sleep Mode, $V_{DD} = 1.8 V \text{ to } 3.6 V$ (Regulator on) SID31 IDD26 I ² C wakeup and WDT on. - 1.3 - μA T = 25 °C SID32 IDD27 I ² C wakeup and WDT on. - - 45 μA T = 85 °C Deep Sleep Mode, $V_{DD} = 3.6 V \text{ to } 5.5 V$ SID34 IDD29 I ² C wakeup and WDT on - 1.5 15 μA Typ. at 25 °C SID34 IDD29 I ² C wakeup and WDT on - 1.7 - μA T = 25 °C SID37 IDD32 I ² C wakeup and WDT on - 1.7 - μA T = 25 °C SID38 IDD33 I ² C wakeup and WDT on - 1.7 - μA T = 25 °C SID38 IDD33 I ² C wakeup and WDT on - - 60 μA T	SID17	I _{DD12}		_	-	7.2	mA	
InterpretationInterpretationInterpretationInterpretationSID25AID20AI²C wakeup, WDT, and Comparators on. 12 MHz1.72.2mA $V_{DD} = 1.71 V \text{ to } 5.5 V$ Deep Sleep Mode, $V_{DD} = 1.8 V \text{ to } 3.6 V$ (Regulator on)SID31ID26I²C wakeup and WDT on1.3- μ AT = 25 °CSID32ID27I²C wakeup and WDT on45 μ AT = 85 °CDeep Sleep Mode, $V_{DD} = 3.6 V \text{ to } 5.5 V$ SID34ID29I²C wakeup and WDT on-1.515 μ ATyp. at 25 °CDeep Sleep Mode, $V_{DD} = 1.71 V \text{ to } 1.89 V$ (Regulator bypassed)SID34ID29I²C wakeup and WDT on-1.7- μ AT = 25 °CSID37ID22I²C wakeup and WDT on-1.7- μ AT = 25 °CSID38ID23I²C wakeup and WDT on60 μ AT = 85 °CDeep Sleep Mode, +105 °CSID38ID23I²C wakeup and WDT on135 μ A $V_{DD} = 1.71 V \text{ to } 1.89 V$ SID33QID23QI²C wakeup and WDT on135 μ A $V_{DD} = 1.71 V \text{ to } 1.89 V$ SID34QID23QI²C wakeup and WDT on135 μ A $V_{DD} = 1.8 V \text{ to } 3.6 V$ SID34QID23QI²C wakeup and WDT on135 μ A $V_{DD} = 1.8 V \text{ to } 3.6 V$	Sleep Mode,	V _{DD} = 1.7 V to 5	.5 V			1		I
DEEXand Comparators on. 12 MHz.DEDeep Sleep Mode, $V_{DD} = 1.8$ V to 3.6 V (Regulator on)SID31 I_{DD26} I^2C wakeup and WDT on. $ 1.3$ $ \mu A$ $T = 25 °C$ SID32 I_{DD27} I^2C wakeup and WDT on. $ 45$ μA $T = 85 °C$ Deep Sleep Mode, $V_{DD} = 3.6$ V to 5.5 VSID34 I_{DD29} I^2C wakeup and WDT on $ 1.5$ 15 μA Typ. at 25 °CDeep Sleep Mode, $V_{DD} = 1.71$ V to 1.89 V (Regulator bypassed)SID37 I_{DD32} I^2C wakeup and WDT on $ 1.7$ $ \mu A$ $T = 25 °C$ SID38 I_{DD33} I^2C wakeup and WDT on $ 60$ μA $T = 85 °C$ Deep Sleep Mode, $\star 105 °C$ SID33Q I_{DD28Q} I^2C wakeup and WDT on. Regulator Off. $ 135$ μA $V_{DD} = 1.71$ V to 1.89 VSID34Q I_{DD28Q} I^2C wakeup and WDT on. Regulator Off. $ 135$ μA $V_{DD} = 1.8$ V to 3.6 V	SID25	I _{DD20}		-	1.3	1.8	mA	V _{DD} = 1.71 V to 5.5 V
SID31 I_{DD26} I^2C wakeup and WDT on1.3- μA T = 25 °CSID32 I_{DD27} I^2C wakeup and WDT on45 μA T = 85 °CDeep Sleep Mode, V_{DD} = 3.6 V to 5.5 VSID34 I_{DD29} I^2C wakeup and WDT on-1.515 μA Typ. at 25 °C Max at 85 °CDeep Sleep Mode, V_{DD} = 1.71 V to 1.89 V (Regulator bypassed)SID37 I_{DD32} I^2C wakeup and WDT on1.7- μA T = 25 °CSID38 I_{DD33} I^2C wakeup and WDT on60 μA T = 85 °CDeep Sleep Mode, +105 °CSID33Q I_{DD28Q} I^2C wakeup and WDT on. Regulator Off135 μA V_{DD} = 1.71 V to 1.89 VSID34Q I_{DD29Q} I^2C wakeup and WDT on. Regulator Off135 μA V_{DD} = 1.8 V to 3.6 V	SID25A	I _{DD20A}		-	1.7	2.2	mA	V _{DD} = 1.71 V to 5.5 V
SID32 I_{DD27} I^2C wakeup and WDT on. $ 45$ μA $T = 85 °C$ Deep Sleep Mode, $V_{DD} = 3.6 V$ to 5.5 VSID34 I_{DD29} I^2C wakeup and WDT on $ 1.5$ 15 μA Typ. at 25 °CDeep Sleep Mode, $V_{DD} = 1.71 V$ to 1.89 V (Regulator bypassed)SID37 I_{DD32} I^2C wakeup and WDT on. $ 1.7$ $ \mu A$ $T = 25 °C$ SID37 I_{DD32} I^2C wakeup and WDT on. $ 60$ μA $T = 85 °C$ Deep Sleep Mode, +105 °CSID33Q I_{DD28Q} I^2C wakeup and WDT on. Regulator Off. $ 135$ μA $V_{DD} = 1.71 V$ to 1.89 VSID38 I_{DD230} I^2C wakeup and WDT on. Regulator Off. $ 135$ μA $V_{DD} = 1.71 V$ to 1.89 VSID33Q I_{DD28Q} I^2C wakeup and WDT on. Regulator Off. $ 135$ μA $V_{DD} = 1.71 V$ to 1.89 VSID34Q I_{DD29Q} I^2C wakeup and WDT on. $ 180$ μA $V_{DD} = 1.8 V$ to $3.6 V$	Deep Sleep N	Mode, V _{DD} = 1.8	V to 3.6 V (Regulator on)			I	1	
Deep Sleep Mode, $V_{DD} = 3.6 \text{ V}$ to 5.5 VSID34 I_{DD29} I^2C wakeup and WDT on-1.515 μA Typ. at 25 °C Max at 85 °CDeep Sleep Mode, $V_{DD} = 1.71 \text{ V}$ to 1.89 V (Regulator bypassed)SID37 I_{DD32} I^2C wakeup and WDT on1.7- μA T = 25 °CSID38 I_{DD33} I^2C wakeup and WDT on60 μA T = 85 °CDeep Sleep Mode, +105 °CSID33Q I_{DD28Q} I^2C wakeup and WDT on. Regulator Off135 μA $V_{DD} = 1.71 \text{ V}$ to 1.89 VSID34Q I_{DD29Q} I^2C wakeup and WDT on130 μA $V_{DD} = 1.8 \text{ V}$ to 3.6 V	SID31	I _{DD26}	I ² C wakeup and WDT on.	_	1.3	_	μA	T = 25 °C
SID34 I_{DD29} I^2C wakeup and WDT on-1.515 μA Typ. at 25 °C Max at 85 °CDeep Sleep Mode, $V_{DD} = 1.71$ V to 1.89 V (Regulator bypassed)SID37 I_{DD32} I^2C wakeup and WDT on1.7- μA T = 25 °CSID38 I_{DD33} I^2C wakeup and WDT on60 μA T = 85 °CDeep Sleep Mode, +105 °CSID33Q I_{DD28Q} I^2C wakeup and WDT on. Regulator Off135 μA $V_{DD} = 1.71$ V to 1.89 VSID34Q I_{DD29Q} I^2C wakeup and WDT on180 μA $V_{DD} = 1.8$ V to 3.6 V	SID32	I _{DD27}	I ² C wakeup and WDT on.	_	1	45	μA	T = 85 °C
Max at 85 °CMax at 85 °CDeep Sleep Mode, $V_{DD} = 1.71$ V to 1.89 V (Regulator bypassed)SID37 I_{DD32} I^2C wakeup and WDT on. $ 1.7$ $ \mu A$ $T = 25$ °CSID38 I_{DD33} I^2C wakeup and WDT on $ 60$ μA $T = 85$ °CDeep Sleep Mode, +105 °CSID33Q I_{DD28Q} I^2C wakeup and WDT on. Regulator Off. $ 135$ μA $V_{DD} = 1.71$ V to 1.89 VSID34Q I_{DD29Q} I^2C wakeup and WDT on. $ 180$ μA $V_{DD} = 1.8$ V to 3.6 V	Deep Sleep N	Mode, V _{DD} = 3.6	V to 5.5 V					
SID37 I_{DD32} I^2C wakeup and WDT on. $ 1.7$ $ \mu A$ $T = 25 °C$ SID38 I_{DD33} I^2C wakeup and WDT on $ 60$ μA $T = 85 °C$ Deep Sleep Mode, +105 °CSID33Q I_{DD28Q} I^2C wakeup and WDT on. Regulator Off. $ 135$ μA $V_{DD} = 1.71 V$ to $1.89 V$ SID34Q I_{DD29Q} I^2C wakeup and WDT on. $ 180$ μA $V_{DD} = 1.8 V$ to $3.6 V$	SID34	I _{DD29}	I ² C wakeup and WDT on	-	1.5	15	μA	
SID38 I_{DD33} I^2C wakeup and WDT on $ 60$ μA $T = 85 °C$ Deep Sleep Mode, +105 °CSID33Q I_{DD28Q} I^2C wakeup and WDT on. Regulator Off. $ 135$ μA $V_{DD} = 1.71 V$ to $1.89 V$ SID34Q I_{DD29Q} I^2C wakeup and WDT on. $ 180$ μA $V_{DD} = 1.8 V$ to $3.6 V$	Deep Sleep N	Mode, V _{DD} = 1.7 ⁴	V to 1.89 V (Regulator bypassed)					
Deep Sleep Mode, +105 °CSID33Q I_{DD28Q} I^2C wakeup and WDT on. Regulator Off. $ -$ 135 μA V_{DD} = 1.71 V to 1.89 VSID34Q I_{DD29Q} I^2C wakeup and WDT on. $ -$ 180 μA V_{DD} = 1.8 V to 3.6 V	SID37	I _{DD32}	I ² C wakeup and WDT on.	_	1.7	_	μA	T = 25 °C
SID33Q I_{DD28Q} I^2C wakeup and WDT on. Regulator Off135 μA $V_{DD} = 1.71$ V to 1.89 VSID34Q I_{DD29Q} I^2C wakeup and WDT on180 μA $V_{DD} = 1.8$ V to 3.6 V	SID38	I _{DD33}	I ² C wakeup and WDT on	-	-	60	μA	T = 85 °C
SID34Q I_{DD29Q} I^2C wakeup and WDT on. $ -$ 180 μ A V_{DD} = 1.8 V to 3.6 V	Deep Sleep N	Mode, +105 °C						
SID34Q I_{DD29Q} I^2C wakeup and WDT on 180 μ A $V_{DD} = 1.8$ V to 3.6 V	SID33Q	I _{DD28Q}	I ² C wakeup and WDT on. Regulator Off.	-	-	135	μA	V _{DD} = 1.71 V to 1.89 V
SID35Q I_{DD30Q} I^2C wakeup and WDT on. - - 140 μA V_{DD} = 3.6 V to 5.5 V	SID34Q	1.	I ² C wakeup and WDT on.	-	—	180	μA	V _{DD} = 1.8 V to 3.6 V
	SID35Q	I _{DD30Q}	I ² C wakeup and WDT on.	-	-	140	μA	V _{DD} = 3.6 V to 5.5 V



Table 3. DC Specifications (continued)

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
Hibernate Mo	ode, V _{DD} = 1.8 V	to 3.6 V (Regulator on)	•				
SID40	I _{DD35}	GPIO & Reset active	-	150	-	nA	T = 25 °C
SID41	I _{DD36}	GPIO & Reset active	-	-	1000	nA	T = 85 °C
Hibernate Mo	ode, V _{DD} = 3.6 V	to 5.5 V					
SID43	I _{DD38}	GPIO & Reset active	-	150	-	nA	T = 25 °C
Hibernate Mo	ode, V _{DD} = 1.71	V to 1.89 V (Regulator bypassed)					
SID46	I _{DD41}	GPIO & Reset active	-	150	-	nA	T = 25 °C
SID47	I _{DD42}	GPIO & Reset active	-	-	1000	nA	T = 85 °C
Hibernate Mo	ode, +105 °C						
SID42Q	I _{DD37Q}	Regulator Off	-	-	19.4	μA	V _{DD} = 1.71 V to 1.89 V
SID43Q	I _{DD38Q}		-	-	17	μA	V _{DD} = 1.8 V to 3.6 V
SID44Q	I _{DD39Q}		-	-	16	μA	V _{DD} = 3.6 V to 5.5 V
Stop Mode							
SID304	I _{DD43A}	Stop Mode current; V _{DD} = 3.3 V	-	20	80	nA	Typ at 25 °C. Max at 85 °C
		Stop Mode current; V _{DD} = 5.5 V	-	20	750	nA	Typ at 25 °C Max at 85 °C
Stop Mode, -	-105 °C	·			•	•	•
SID304Q	I _{DD43AQ}	Stop Mode current; V _{DD} = 3.6 V	-	_	5645	nA	
XRES currer	nt	·			•	•	•
SID307	I _{DD_XR}	Supply current while XRES asserted	-	2	5	mA	



GPIO

Table 4. GPIO DC Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/ Conditions
SID57	V _{IH} [2]	Input voltage high threshold	0.7 × V _{DDD}	_	-	V	CMOS Input
SID58	V _{IL}	Input voltage low threshold	-	_	0.3 × V _{DDD}	V	CMOS Input
SID241	V _{IH} ^[2]	LVTTL input, V _{DDD} < 2.7 V	0.7× V _{DDD}	_	-	V	
SID242	V _{IL}	LVTTL input, V _{DDD} < 2.7 V	-	-	0.3 × V _{DDD}	V	
SID243	V _{IH} ^[2]	LVTTL input, $V_{DDD} \ge 2.7 V$	2.0	-	_	V	
SID244	V _{IL}	LVTTL input, $V_{DDD} \ge 2.7 V$	_	-	0.8	V	
SID59	V _{OH}	Output voltage high level	V _{DDD} -0.6	-	-	V	I _{OH} = 4 mA at 3 V V _{DDD}
SID60	V _{OH}	Output voltage high level	V _{DDD} -0.5	-	_	V	I _{OH} = 1 mA at 1.8 V V _{DDD}
SID61	V _{OL}	Output voltage low level	-	-	0.6	V	I _{OL} = 4 mA at 1.8 V V _{DDD}
SID62	V _{OL}	Output voltage low level	-	-	0.6	V	I _{OL} = 8 mA at 3 V V _{DDD}
SID62A	V _{OL}	Output voltage low level	-	-	0.4	V	I _{OL} = 3 mA at 3 V V _{DDD}
SID63	R _{PULLUP}	Pull-up resistor	3.5	5.6	8.5	kΩ	
SID64	R _{PULLDOWN}	Pull-down resistor	3.5	5.6	8.5	kΩ	
SID65	IIL	Input leakage current (absolute value)	-	-	2	nA	25 °C, V _{DDD} = 3.0 V
SID65A	I _{IL_CTBM}	Input leakage current (absolute value) for CTBM pins	-	-	4	nA	
SID66	C _{IN}	Input capacitance	-	-	7	pF	
SID67	V _{HYSTTL}	Input hysteresis LVTTL	25	40	-	mV	$V_{DDD} \ge 2.7 V.$ Guaranteed by characterization
SID68	V _{HYSCMOS}	Input hysteresis CMOS	0.05 × V _{DDD}	_	-	mV	Guaranteed by characterization
SID69	I _{DIODE}	Current through protection diode to V _{DD} /Vss	-	-	100	μA	Guaranteed by characterization
SID69A	I _{TOT_GPIO}	Maximum total source or sink chip current	-	-	200	mA	Guaranteed by characterization



Spec ID#	Parameter	Description	Min	Тур	Мах	Units	Details/ Conditions
SID70	T _{RISEF}	Rise time in fast strong mode	2	-	12	ns	3.3-V V _{DDD} , Cload = 25 pF
SID71	T _{FALLF}	Fall time in fast strong mode	2	-	12	ns	3.3-V V _{DDD} , Cload = 25 pF
SID72	T _{RISES}	Rise time in slow strong mode	10	-	60		3.3-V V _{DDD} , Cload = 25 pF
SID73	T _{FALLS}	Fall time in slow strong mode	10	-	60		3.3-V V _{DDD} , Cload = 25 pF
SID74	F _{GPIOUT1}	GPIO Fout;3.3 V \leq V _{DDD} \leq 5.5 V. Fast strong mode.	_	-	24	MHz	90/10%, 25-pF load, 60/40 duty cycle
SID75	F _{GPIOUT2}	GPIO Fout;1.7 V≤ V _{DDD} ≤ 3.3 V. Fast strong mode.	_	-	16.7	MHz	90/10%, 25-pF load, 60/40 duty cycle
SID76	F _{GPIOUT3}	GPIO Fout;3.3 V \leq V _{DDD} \leq 5.5 V. Slow strong mode.	-	-	7	MHz	90/10%, 25-pF load, 60/40 duty cycle
SID245	F _{GPIOUT4}	GPIO Fout;1.7 V \leq V _{DDD} \leq 3.3 V. Slow strong mode.	_	-	3.5	MHz	90/10%, 25-pF load, 60/40 duty cycle
SID246	F _{GPIOIN}	GPIO input operating frequency; 1.71 V \leq V _{DDD} \leq 5.5 V	_	-	24	MHz	90/10% V _{IO}

Table 5. GPIO AC Specifications (Guaranteed by Characterization)

XRES

Table 6. XRES DC Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/ Conditions
SID77	V _{IH}	Input voltage high threshold	0.7 × V _{DDD}	-	-	V	CMOS Input
SID78	V _{IL}	Input voltage low threshold	-	-	0.3 × V _{DDD}	V	CMOS Input
SID79	R _{PULLUP}	Pull-up resistor	3.5	5.6	8.5	kΩ	
SID80	C _{IN}	Input capacitance	-	3	-	pF	
SID81	V _{HYSXRES}	Input voltage hysteresis	-	100	-	mV	Guaranteed by characterization
SID82	I _{DIODE}	Current through protection diode to V_{DDD}/V_{SS}	_	_	100	μA	Guaranteed by characterization

Table 7. XRES AC Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/ Conditions
SID83	T _{RESETWIDTH}	Reset pulse width	1	-	-		Guaranteed by characterization



Analog Peripherals

Opamp

Table 8. Opamp Specifications (Guaranteed by Characterization)

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/ Conditions
	I _{DD}	Opamp block current. No load.	-	-	-	-	
SID269	I _{DD_HI}	Power = high	-	1100	1850	μA	
SID270	I _{DD_MED}	Power = medium	-	550	950	μA	
SID271	I _{DD_LOW}	Power = low	-	150	350	μA	
	GBW	Load = 20 pF, 0.1 mA. V _{DDA} = 2.7 V	-	-	-	_	
SID272	GBW_HI	Power = high	6	-	-	MHz	
SID273	GBW_MED	Power = medium	4	-	-	MHz	
SID274	GBW_LO	Power = low	-	1	-	MHz	
	I _{OUT_MAX}	$V_{DDA} \ge 2.7 \text{ V}, 500 \text{ mV}$ from rail	-	-	_	_	
SID275	I _{OUT_MAX_HI}	Power = high	10	-	_	mA	
SID276	I _{OUT_MAX_MID}	Power = medium	10	-	_	mA	
SID277	I _{OUT_MAX_LO}	Power = low	-	5	-	mA	
	I _{OUT}	V _{DDA} = 1.71 V, 500 mV from rail	_	-	_	_	
SID278	I _{OUT_MAX_HI}	Power = high	4	-	-	mA	
SID279	I _{OUT_MAX_MID}	Power = medium	4	-	-	mA	
SID280	IOUT MAX LO	Power = low	-	2	-	mA	
SID281	V _{IN}	Charge pump on, $V_{DDA} \ge 2.7 V$	-0.05	-	V _{DDA} – 0.2	V	
SID282	V _{CM}	Charge pump on, $V_{DDA} \ge 2.7 V$	-0.05	_	V _{DDA} - 0.2	V	
	V _{OUT}	$V_{DDA} \ge 2.7 V$	-	-	-		
SID283	V _{OUT_1}	Power = high, Iload=10 mA	0.5	-	V _{DDA} – 0.5	V	
SID284	V _{OUT_2}	Power = high, lload=1 mA	0.2	-	V _{DDA} - 0.2	V	
SID285	V _{OUT_3}	Power = medium, lload=1 mA	0.2	-	V _{DDA} - 0.2	V	
SID286	V _{OUT_4}	Power = low, lload=0.1mA	0.2	-	V _{DDA} – 0.2	V	
SID288	V _{OS_TR}	Offset voltage, trimmed	1	±0.5	1	mV	High mode
SID288A	V _{OS_TR}	Offset voltage, trimmed	-	±1	-	mV	Medium mode
SID288B	V _{OS_TR}	Offset voltage, trimmed	-	±2	-	mV	Low mode
SID290	V _{OS_DR_TR}	Offset voltage drift, trimmed	-10	±3	10	µV/°C	High mode T _A <u><</u> 85 °C.
SID290Q	V _{OS_DR_TR}	Offset voltage drift, trimmed	-15	±3	15	µV/°C	High mode. T _A ≤ 105 °C
SID290A	V _{OS_DR_TR}	Offset voltage drift, trimmed	-	±10	-	µV/°C	Medium mode
SID290B	V _{OS_DR_TR}	Offset voltage drift, trimmed	_	±10	_		Low mode
SID291	CMRR	DC	70	80	-	dB	V _{DDD} = 3.6 V
SID292	PSRR	At 1 kHz, 100 mV ripple	70	85	_	dB	V _{DDD} = 3.6 V
	Noise		_	_	_	_	
SID293	V _{N1}	Input referred, 1 Hz - 1GHz, power = high	-	94	-	µVrms	
SID294	V _{N2}	Input referred, 1 kHz, power = high	-	72	-	nV/rtHz	
SID295	V _{N3}	Input referred, 10 kHz, power = high	_	28	_	nV/rtHz	
SID296	V _{N4}	Input referred, 100 kHz, power = high	_	15	_	nV/rtHz	



Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/ Conditions
SID297	Cload	Stable up to maximum load. Perfor- mance specs at 50 pF.	-	-	125	pF	
SID298	Slew_rate	Cload = 50 pF, Power = High, $V_{DDA} \ge$ 2.7 V	6	-	_	V/µs	
SID299	T_op_wake	From disable to enable, no external RC dominating	-	300	-	μs	
	Comp_mode	Comparator mode; 50 mV drive, Trise = Tfall (approx.)	-	-	-		
SID299A	OL_GAIN	Open Loop Gain	-	90	-	dB	Guaranteed by design
SID300	T _{PD1}	Response time; power = high	_	150	_	ns	
SID301	T _{PD2}	Response time; power = medium	-	400	-	ns	
SID302	T _{PD3}	Response time; power = low	_	2000	_	ns	
SID303	Vhyst_op	Hysteresis	_	10	_	mV	

Table 8. Opamp Specifications (Guaranteed by Characterization) (continued)

Comparator

Table 9. Comparator DC Specifications

Spec ID#	Parameter	Description	Min	Тур	Мах	Units	Details/ Conditions
SID85	V _{OFFSET2}	Input offset voltage, Common Mode voltage range from 0 to V _{DD} -1	-	-	±4	mV	
SID85A	V _{OFFSET3}	Input offset voltage. Ultra low-power mode ($V_{DDD} \ge 2.2 \text{ V}$ for Temp < 0 °C, $V_{DDD} \ge 1.8 \text{ V}$ for Temp > 0 °C)	-	±12	-	mV	
SID86	V _{HYST}	Hysteresis when enabled, Common Mode voltage range from 0 to $(V_{DD} - 1)$.	-	10	35	mV	Guaranteed by characterization
SID87	V _{ICM1}	Input common mode voltage in normal mode	0	-	V _{DDD} – 0.1	V	Modes 1 and 2
SID247	V _{ICM2}	Input common mode voltage in low power mode ($V_{DDD} \ge 2.2 \text{ V}$ for Temp < 0 °C, $V_{DDD} \ge 1.8 \text{ V}$ for Temp > 0 °C)	0	-	V _{DDD}	V	
SID247A	V _{ICM3}	Input common mode voltage in ultra low power mode	0	-	V _{DDD} – 1.15	V	
SID88	CMRR	Common mode rejection ratio	50	-	-	dB	$V_{DDD} \ge 2.7 V.$ Guaranteed by characterization
SID88A	CMRR	Common mode rejection ratio	42	-	-	dB	V _{DDD} < 2.7 V. Guaranteed by characterization
SID89	I _{CMP1}	Block current, normal mode	-	-	400	μA	Guaranteed by characterization
SID248	I _{CMP2}	Block current, low power mode	-	-	100	μA	Guaranteed by characterization
SID259	I _{CMP3}	Block current, ultra low power mode ($V_{DDD} \ge 2.2 \text{ V}$ for Temp < 0 °C, $V_{DDD} \ge 1.8 \text{ V}$ for Temp > 0 °C)	-	6	28	μA	Guaranteed by characterization
SID90	Z _{CMP}	DC input impedance of comparator	35	-	-	MΩ	Guaranteed by characterization



Table 10. Comparator AC Specifications

(Guaranteed by Characterization)

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID91	T _{RESP1}	Response time, normal mode	-	-	110	ns	50 mV overdrive
SID258	T _{RESP2}	Response time, low power mode	-	-	200	ns	50 mV overdrive
SID92		Response time, ultra low power mode ($V_{DDD} \ge 2.2 \text{ V}$ for Temp < 0 °C, $V_{DDD} \ge 1.8 \text{ V}$ for Temp > 0 °C)	Ι	-	15	μs	200 mV overdrive

Temperature Sensor

Table 11. Temperature Sensor Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID93	T _{SENSACC}	Temperature sensor accuracy	-5	±1	+5	°C	–40 to +85 °C

SAR ADC

Table 12. SAR ADC DC Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID94	A_RES	Resolution	-	-	12	bits	
SID95	A_CHNIS_S	Number of channels - single ended	-	-	8		8 full speed
SID96	A-CHNKS_D	Number of channels - differential	-	-	4		Diff inputs use neighboring I/O
SID97	A-MONO	Monotonicity	-	-	_		Yes. Based on characterization
SID98	A_GAINERR	Gain error	-	-	±0.1	%	With external reference. Guaranteed by characterization
SID99	A_OFFSET	Input offset voltage	-		2	mV	Measured with 1-V V _{REF.} Guaranteed by characterization
SID100	A_ISAR	Current consumption	_	-	1	mA	
SID101	A_VINS	Input voltage range - single ended	V _{SS}	-	V _{DDA}	V	Based on device characterization
SID102	A_VIND	Input voltage range - differential	V _{SS}	-	V _{DDA}	V	Based on device characterization
SID103	A_INRES	Input resistance	-	-	2.2	KΩ	Based on device characterization
SID104	A_INCAP	Input capacitance	-	-	10	pF	Based on device characterization



Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID106	A_PSRR	Power supply rejection ratio	70	-	_	dB	
SID107	A_CMRR	Common mode rejection ratio	66	-	-	dB	Measured at 1 V
SID108	A_SAMP_1	Sample rate with external reference bypass cap	-	-	1	Msps	
SID108A	A_SAMP_2	Sample rate with no bypass cap. Reference = V _{DD}	_	-	806	Ksps	
SID108B	A_SAMP_3	Sample rate with no bypass cap. Internal reference	-	-	100	Ksps	
SID109	A_SNDR	Signal-to-noise and distortion ratio (SINAD)	65	-	-	dB	F _{IN} = 10 kHz
SID111	A_INL	Integral non linearity	-1.7	-	+2	LSB	$\begin{array}{l} V_{DD} = 1.71 \ to \ 5.5, \ 806 \\ Ksps, \ Vref = 1 \ to \ 5.5. \\ -40 \ ^{\circ}C \leq \ T_A \ \leq \ 85 \ ^{\circ}C \end{array}$
			-1.9	_	+2	LSB	$\begin{array}{l} V_{DD} = 1.71 \ to \ 5.5, \ 806 \\ Ksps, \ Vref = 1 \ to \ 5.5. \\ -40 \ ^{\circ}C \leq \ T_A \leq \ 105 \ ^{\circ}C \end{array}$
SID111A	A_INL	Integral non linearity	-1.5	_	+1.7	LSB	$\begin{array}{l} V_{DDD} = 1.71 \ \text{to} \ 3.6, \\ 806 \ \text{Ksps}, \ \text{Vref} = 1.71 \\ \text{to} \ \text{V}_{DDD}. \ -40 \ ^\circ\text{C} \leq \ \text{T}_{\text{A}} \\ \leq \ 85 \ ^\circ\text{C} \end{array}$
			-1.9	_	+2	LSB	$\begin{array}{l} V_{DDD} = 1.71 \ \text{to} \ 3.6, \\ 806 \ \text{Ksps}, \ \text{Vref} = 1.71 \\ \text{to} \ V_{DDD}. \ -40 \ ^{\circ}\text{C} \leq \ \text{T}_{\text{A}} \\ \leq \ 105 \ ^{\circ}\text{C} \end{array}$
SID111B	A_INL	Integral non linearity	-1.5	-	+1.7	LSB	V _{DDD} = 1.71 to 5.5, 500 Ksps, Vref = 1 to 5.5.
SID112	A_DNL	Differential non linearity	-1	_	+2.2	LSB	$\begin{array}{l} V_{DDD} \mbox{=} 1.71 \mbox{ to } 5.5, \\ 806 \mbox{ Ksps}, \mbox{ Vref = 1 to} \\ 5.5. \ \ -40 \ \ ^{\circ}C \ \le \ \ T_A \ \le \\ 85 \ \ ^{\circ}C \end{array}$
			–1	_	+2.3	LSB	$\begin{array}{l} V_{DDD} \mbox{=} 1.71 \mbox{ to } 5.5, \\ 806 \mbox{ Ksps}, \mbox{ Vref = 1 to} \\ 5.5. \ -40 \ ^{\circ}C \ \leq \ T_A \ \leq \\ 105 \ ^{\circ}C \end{array}$
SID112A	A_DNL	Differential non linearity	-1	_	+2	LSB	$\begin{array}{l} V_{DDD} = 1.71 \ \text{to} \ 3.6, \\ 806 \ \text{Ksps}, \ \text{Vref} = 1.71 \\ \text{to} \ V_{DDD}. \ -40 \ ^{\circ}\text{C} \leq \ \text{T}_{\text{A}} \\ \leq \ 85 \ ^{\circ}\text{C} \end{array}$
			-1	_	+2.2	LSB	$\begin{array}{l} V_{DDD} = 1.71 \ \text{to} \ 3.6, \\ 806 \ \text{Ksps}, \ \text{Vref} = 1.71 \\ \text{to} \ V_{DDD}. \ -40 \ ^{\circ}\text{C} \leq \ \text{T}_{\text{A}} \\ \leq \ 105 \ ^{\circ}\text{C} \end{array}$
SID112B	A_DNL	Differential non linearity	-1	-	+2.2	LSB	V _{DDD} = 1.71 to 5.5, 500 Ksps, Vref = 1 to 5.5.
SID113	A_THD	Total harmonic distortion	_	-	-65	dB	F _{IN} = 10 kHz.

Table 13. SAR ADC AC Specifications (Guaranteed by Characterization)



CSD

Table 14. CSD Block Specification

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/ Conditions
CSD Spe	cification						
SID308	VCSD	Voltage range of operation	1.71	-	5.5	V	
SID309	IDAC1	DNL for 8-bit resolution	-1	-	1	LSB	
SID310	IDAC1	INL for 8-bit resolution	-3	-	3	LSB	
SID311	IDAC2	DNL for 7-bit resolution	-1	-	1	LSB	
SID312	IDAC2	INL for 7-bit resolution	-3	-	3	LSB	
SID313	SNR	Ratio of counts of finger to noise. Guaranteed by characterization	5	-	I	Ratio	Capacitance range of 9 to 35 pF, 0.1 pF sensitivity
SID314	IDAC1_CRT1	Output current of Idac1 (8-bits) in High range	I	612	Ι	μA	
SID314A	IDAC1_CRT2	Output current of Idac1(8-bits) in Low range	I	306	Ι	μA	
SID315	IDAC2_CRT1	Output current of Idac2 (7-bits) in High range	I	304.8	I	μA	
SID315A	IDAC2_CRT2	Output current of Idac2 (7-bits) in Low range	I	152.4	I	μA	

Digital Peripherals

The following specifications apply to the Timer/Counter/PWM peripherals in the Timer mode.

Timer/Counter/PWM

Table 15. TCPWM Specifications

(Guaranteed by Characterization)

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID.TCPWM.1	ITCPWM1	Block current consumption at 3 MHz	-	-	45	μA	All modes (Timer/Counter/PWM)
SID.TCPWM.2	ITCPWM2	Block current consumption at 12 MHz	-	-	155	μA	All modes (Timer/Counter/PWM)
SID.TCPWM.2A	ITCPWM3	Block current consumption at 48 MHz	-	-	650	μA	All modes (Timer/Counter/PWM)
SID.TCPWM.3	TCPWMFREQ	Operating frequency	-	-	Fc	MHz	Fc max = Fcpu. Maximum = 24 MHz
SID.TCPWM.4	TPWMENEXT	Input Trigger Pulse Width for all Trigger Events	2/Fc	-	-	ns	Trigger Events can be Stop, Start, Reload, Count, Capture, or Kill depending on which mode of operation is selected.
SID.TCPWM.5	TPWMEXT	Output Trigger Pulse widths	2/Fc	-	-	ns	Minimum possible width of Overflow, Underflow, and CC (Counter equals Compare value) trigger outputs
SID.TCPWM.5A	TCRES	Resolution of Counter	1/Fc	-	Ι	ns	Minimum time between successive counts
SID.TCPWM.5B	PWMRES	PWM Resolution	1/Fc	-	-	ns	Minimum pulse width of PWM Output
SID.TCPWM.5C	QRES	Quadrature inputs resolution	1/Fc	_	_	ns	Minimum pulse width between Quadrature phase inputs.



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Table 16. Fixed I²C DC Specifications (Guaranteed by Characterization)

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID149	I _{I2C1}	Block current consumption at 100 kHz	-	-	50	μA	
SID150	I _{I2C2}	Block current consumption at 400 kHz	-	-	135	μA	
SID151	I _{I2C3}	Block current consumption at 1 Mbps	-	-	310	μA	
SID152	I _{I2C4}	I ² C enabled in Deep Sleep mode	-	-	1.4	μA	

Table 17. Fixed I²C AC Specifications (Guaranteed by Characterization)

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID153	F _{I2C1}	Bit rate	-	—	1	Mbps	

LCD Direct Drive

Table 18. LCD Direct Drive DC Specifications (Guaranteed by Characterization)

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID154	ILCDLOW	Operating current in low power mode	-	5	-	μA	16 × 4 small segment disp. at 50 Hz
SID155	C _{LCDCAP}	LCD capacitance per segment/common driver	_	500	5000	pF	Guaranteed by Design
SID156	LCD _{OFFSET}	Long-term segment offset	-	20	-	mV	
SID157	I _{LCDOP1}	PWM Mode current. 5-V bias. 24-MHz IMO. 25 °C	-	0.6	-	mA	32 × 4 segments. 50 Hz
SID158	I _{LCDOP2}	PWM Mode current. 3.3-V bias. 24-MHz IMO. 25 °C	_	0.5	_	mA	32 × 4 segments. 50 Hz

Table 19. LCD Direct Drive AC Specifications (Guaranteed by Characterization)

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID159	F _{LCD}	LCD frame rate	10	50	150	Hz	

Table 20. Fixed UART DC Specifications (Guaranteed by Characterization)

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID160	I _{UART1}	Block current consumption at 100 Kbits/sec	-	-	55	μA	
SID161	I _{UART2}	Block current consumption at 1000 Kbits/sec	-	-	312	μA	

Table 21. Fixed UART AC Specifications (Guaranteed by Characterization)

Spec ID	Parameter	Description	Min	Тур	Max	Units
SID162	F _{UART}	Bit rate	_	-	1	Mbps



SPI Specifications

Table 22. Fixed SPI DC Specifications (Guaranteed by Characterization)

Spec ID	Parameter Description		Min	Тур	Max	Units
SID163	I _{SPI1}	Block current consumption at 1 Mbits/sec	-	-	360	μA
SID164	I _{SPI2}	Block current consumption at 4 Mbits/sec	-	-	560	μA
SID165	I _{SPI3}	Block current consumption at 8 Mbits/sec	-	-	600	μA

Table 23. Fixed SPI AC Specifications (Guaranteed by Characterization)

Spec ID	Parameter	Description	Min	Тур	Max	Units
SID166	011	SPI operating frequency (master; 6X oversampling)	-	-	4	MHz

Table 24. Fixed SPI Master mode AC Specifications (Guaranteed by Characterization)

Spec ID	Parameter	Description	Min	Тур	Max	Units
SID167	T _{DMO}	MOSI valid after Sclock driving edge	_	-	15	ns
SID168	T _{DSI}	MISO valid before Sclock capturing edge. Full clock, late MISO Sampling used	20	-	-	ns
SID169	T _{HMO}	Previous MOSI data hold time with respect to capturing edge at Slave	0	-	-	ns

Table 25. Fixed SPI Slave mode AC Specifications (Guaranteed by Characterization)

Spec ID	Parameter	Description	Min	Тур	Max	Units
SID170	T _{DMI}	MOSI valid before Sclock capturing edge	40	-	-	ns
SID171	T _{DSO}	MISO valid after Sclock driving edge	-	-	42 + (3 × Tscbclk)	ns
SID171A	T _{DSO_ext}	MISO valid after Sclock driving edge in Ext. Clock mode	-	-	48	ns
SID172	T _{HSO}	Previous MISO data hold time	0	-	-	ns
SID172A	T _{SSELSCK}	SSEL Valid to first SCK Valid edge	100	-	-	ns



Memory

Table 26. Flash DC Specifications

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID173	V _{PE}	Erase and program voltage	1.71	-	5.5	V	

Table 27. Flash AC Specifications

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID174	T _{ROWWRITE} ^[3]	Row (block) write time (erase and program)	-	-	20	ms	Row (block) = 128 bytes. –40 $^\circ\text{C} \leq \ensuremath{ T_A} \leq \ensuremath{ 85\ ^\circ\text{C}}$
			-	_	26	ms	Row (block) = 128 bytes. –40 $^\circ\text{C} \leq \ \text{T}_{\text{A}} \leq \ 105 \ ^\circ\text{C}$
SID175	T _{ROWERASE} ^[3]	Row erase time	-	-	13	ms	
SID176	T _{ROWPROGRAM} ^[3]	Row program time after erase	-	_	7	ms	-40 °C \leq T _A \leq 85 °C
			-	_	13	ms	-40 °C \leq T _A \leq 105 °C
SID178	T _{BULKERASE} ^[3]	Bulk erase time (32 KB)	-	-	35	ms	
SID180	T _{DEVPROG} ^[3]	Total device program time	-	-	7	seconds	Guaranteed by characterization
SID181	F _{END}	Flash endurance	100 K	-	-	cycles	Guaranteed by characterization
SID182	F _{RET}	Flash retention. $T_A \le 55 \degree$ C, 100 K P/E cycles	20	_	-	years	Guaranteed by characterization
SID182A		Flash retention. $T_A \le 85 \text{ °C}$, 10 K P/E cycles	10	_	-	years	Guaranteed by characterization
SID182B	F _{RETQ}	Flash retention. $T_A \le 105 \text{ °C}$, 10K P/E cycles, \le three years at $T_A \ge 85 \text{ °C}$.	10	20	-		Guaranteed by character- ization.

System Resources

Power-on-Reset (POR) with Brown Out

Table 28. Imprecise Power On Reset (PRES)

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID185	V _{RISEIPOR}	Rising trip voltage	0.80	-	1.45	V	Guaranteed by characterization
SID186	V _{FALLIPOR}	Falling trip voltage	0.75	-	1.4	V	Guaranteed by characterization
SID187	VIPORHYST	Hysteresis	15		200	mV	Guaranteed by characterization

Table 29. Precise Power On Reset (POR)

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID190	V _{FALLPPOR}	BOD trip voltage in active and sleep modes	1.64	_	_		Full functionality between 1.71 V and BOD trip voltage is guaranteed by characterization
SID192	V _{FALLDPSLP}	BOD trip voltage in Deep Sleep	1.4	-	-	V	Guaranteed by characterization
BID55	Svdd	Maximum power supply ramp rate	-	-	67	kV/sec	

Note

It can take as much as 20 milliseconds to write to Flash. During this time the device should not be Reset, or Flash operations will be interrupted and cannot be relied on to have completed. Reset sources include the XRES pin, software resets, CPU lockup states and privilege violations, improper power supply levels, and watchdogs. Make certain that these are not inadvertently activated.



Voltage Monitors

Table 30. Voltage Monitors DC Specifications

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID195	V _{LVI1}	LVI_A/D_SEL[3:0] = 0000b	1.71	1.75	1.79	V	
SID196	V _{LVI2}	LVI_A/D_SEL[3:0] = 0001b	1.76	1.80	1.85	V	
SID197	V _{LVI3}	LVI_A/D_SEL[3:0] = 0010b	1.85	1.90	1.95	V	
SID198	V _{LVI4}	LVI_A/D_SEL[3:0] = 0011b	1.95	2.00	2.05	V	
SID199	V _{LVI5}	LVI_A/D_SEL[3:0] = 0100b	2.05	2.10	2.15	V	
SID200	V _{LVI6}	LVI_A/D_SEL[3:0] = 0101b	2.15	2.20	2.26	V	
SID201	V _{LVI7}	LVI_A/D_SEL[3:0] = 0110b	2.24	2.30	2.36	V	
SID202	V _{LVI8}	LVI_A/D_SEL[3:0] = 0111b	2.34	2.40	2.46	V	
SID203	V _{LVI9}	LVI_A/D_SEL[3:0] = 1000b	2.44	2.50	2.56	V	
SID204	V _{LVI10}	LVI_A/D_SEL[3:0] = 1001b	2.54	2.60	2.67	V	
SID205	V _{LVI11}	LVI_A/D_SEL[3:0] = 1010b	2.63	2.70	2.77	V	
SID206	V _{LVI12}	LVI_A/D_SEL[3:0] = 1011b	2.73	2.80	2.87	V	
SID207	V _{LVI13}	LVI_A/D_SEL[3:0] = 1100b	2.83	2.90	2.97	V	
SID208	V _{LVI14}	LVI_A/D_SEL[3:0] = 1101b	2.93	3.00	3.08	V	
SID209	V _{LVI15}	LVI_A/D_SEL[3:0] = 1110b	3.12	3.20	3.28	V	
SID210	V _{LVI16}	LVI_A/D_SEL[3:0] = 1111b	4.39	4.50	4.61	V	
SID211	LVI_IDD	Block current	_	-	100	μA	Guaranteed by characterization

Table 31. Voltage Monitors AC Specifications

Spec ID	Parameter	Description	Min	Тур	Мах	Units	Details/Conditions
SID212	T _{MONTRIP}	Voltage monitor trip time			1	μs	Guaranteed by characterization

SWD Interface

 Table 32.
 SWD Interface Specifications

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID213	F_SWDCLK1	$3.3 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}$	-	_	14	MHz	SWDCLK ≤ 1/3 CPU clock frequency
SID214	F_SWDCLK2	$1.71 \text{ V} \le \text{V}_{\text{DD}} \le 3.3 \text{ V}$	-	_	7	MHz	SWDCLK ≤ 1/3 CPU clock frequency
SID215	T_SWDI_SETUP	T = 1/f SWDCLK	0.25*T	_	_	ns	Guaranteed by characterization
SID216	T_SWDI_HOLD	T = 1/f SWDCLK	0.25*T	_	_	ns	Guaranteed by characterization
SID217	T_SWDO_VALID	T = 1/f SWDCLK	-	_	0.5*T	ns	Guaranteed by characterization
SID217A	T_SWDO_HOLD	T = 1/f SWDCLK	1	_	_	ns	Guaranteed by characterization



Internal Main Oscillator

Table 33. IMO DC Specifications (Guaranteed by Design)

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID219	I _{IMO2}	IMO operating current at 24 MHz	-	-	325	μA	
SID220	I _{IMO3}	IMO operating current at 12 MHz	-	-	225	μA	
SID221	I _{IMO4}	IMO operating current at 6 MHz	-	-	180	μA	
SID222	I _{IMO5}	IMO operating current at 3 MHz	-	_	150	μA	

Table 34. IMO AC Specifications

Spec ID	Parameter	Description	Min Typ		Max	Units	Details/Conditions
SID223	F _{IMOTOL1}	Frequency variation from 3 to 24 MHz	-	-	±2	%	<u>+</u> 3% if T _A > 85 °C and IMO frequency < 24 MHz
SID226	T _{STARTIMO}	IMO startup time	-	-	12	μs	
SID227	T _{JITRMSIMO1}	RMS Jitter at 3 MHz	-	156	-	ps	
SID228	T _{JITRMSIMO2}	RMS Jitter at 24 MHz	-	145	-	ps	

Internal Low-Speed Oscillator

Table 35. ILO DC Specifications (Guaranteed by Design)

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID231	I _{ILO1}	ILO operating current at 32 kHz	-	0.3	1.05		Guaranteed by Characterization
SID233	I _{ILOLEAK}	ILO leakage current	_	2	15		Guaranteed by Design

Table 36. ILO AC Specifications

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID234	T _{STARTILO1}	ILO startup time	-	_	2	ms	Guaranteed by charac- terization
SID236	T _{ILODUTY}	ILO duty cycle	40	50	60	%	Guaranteed by charac- terization
SID237	F _{ILOTRIM1}	32 kHz trimmed frequency	15	32	50	kHz	Max. ILO frequency is 70 kHz if T _A > 85 °C

Table 37. External Clock Specifications

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID305	ExtClkFreq	External Clock input Frequency	0	-	24		Guaranteed by characterization
SID306	ExtClkDuty	Duty cycle; Measured at $V_{DD/2}$	45	Ι	55		Guaranteed by characterization



Table 38. Block Specs

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID257	T _{WS24} *	Number of wait states at 24 MHz	0	-	-		CPU execution from Flash. Guaranteed by characterization
SID260	V _{REFSAR}	Trimmed internal reference to SAR	-1	-	+1	%	Percentage of Vbg (1.024 V). Guaranteed by characterization
SID262	T _{CLKSWITCH}	Clock switching from clk1 to clk2 in clk1 periods	3	-	4	Periods	Guaranteed by design
* Tws24 is gu	aranteed by design.	1		1	I	1	1



Ordering Information

The PSoC 4100 part numbers and features are listed in the Table 39.

Table 39. PSoC 4100 Family Ordering Information

		Features										Package	Operating Temperature			
Family	MPN	Max CPU Speed (MHz)	Flash (KB)	SRAM (KB)	UDB	Opamp (CTBm)	CapSense	Direct LCD Drive	12-bit SAR ADC	LP Comparators	TCPWM Blocks	SCB Blocks	GPIO	28-SSOP	–40 to +85 °C	–40 to +105 °C
	CY8C4124PVA-442Z	24	16	4	I	1	~	~	806 Ksps	2	4	2	24	~	~	_
4100	CY8C4125PVA-482Z	24	32	4	-	1	~	~	806 Ksps	2	4	2	24	~	~	_
4100	CY8C4124PVS-442Z	24	16	4	-	1	~	~	806 Ksps	2	4	2	24	~	-	~
	CY8C4125PVS-482Z	24	32	4	-	1	~	~	806 Ksps	2	4	2	24	~	_	~

Part Numbering Conventions

PSoC 4 devices follow the part numbering convention described in the following table. All fields are single-character alphanumeric (0, 1, 2, ..., 9, A,B, ..., Z) unless stated otherwise.

The part numbers are of the form CY8C4ABCDEF-GHI where the fields are defined as follows.

Example	<u>CY8C 4 A B C DE F - GHI Z</u>	<u>′</u>
	Cypress Prefix	
4: PSoC4	Architecture	
1: 4100 Family	Family within Architecture	
2: 24 MHz	Speed Grade	
5: 32 KB	Flash Capacity ————————————————————————————————————	
PV: SSOP	Package Code	
A: Automotive -40 to +85 °C S: Automotive: -40 to +105 °C	Temperature Range ————————————————————————————————————	
	Attributes Set	
	Fab Location Change: Z —	



The field values are listed in Table 40.

Table 40. Field Values

Field	Description	Values	Meaning
CY8C	Cypress Prefix		
4	Architecture	4	PSoC 4
Α	Family within architecture	1	4100 Family
		2	4200 Family
В	CPU Speed	2	24 MHz
		4	48 MHz
С	Flash Capacity	4	16 KB
		5	32 KB
DE	Package Code	PV	SSOP
F	Temperature Range	A/S	Automotive
GHI	Attributes Code	000-999	Code of feature set in specific family
Z	Fab location change		

Packaging

Table 41. Package Characteristics

Parameter	Description	Conditions	Min	Тур	Max	Units
T _A	Operating ambient temperature	For A grade devices	-40	25.00	85	°C
T _A	Operating ambient temperature	For S grade devices	-40	25.00	105	°C
TJ	Operating junction temperature	For A grade devices	-40	-	100	°C
TJ	Operating junction temperature	For S grade devices	-40	-	120	°C
T _{JA}	Package θ_{JA} (28-pin SSOP)		-	66.58	-	°C/W
T _{JC}	Package θ_{JC} (28-pin SSOP)		-	46.28	-	°C/W

Table 42. Solder Reflow Peak Temperature

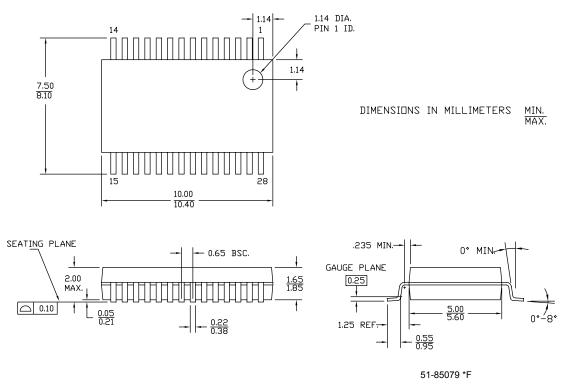
Package	Maximum Peak Temperature	Maximum Time at Peak Temperature
28-pin SSOP	260 °C	30 seconds

Table 43. Package Moisture Sensitivity Level (MSL), IPC/JEDEC J-STD-2

Package	MSL
28-pin SSOP	MSL 3

PSoC4 CAB Libraries with Schematics Symbols and PCB Footprints are on the Cypress web site at http://www.cypress.com/cad-resources/psoc-4-cad-libraries?source=search&cat=technical_documents







Acronyms

Table 44. Acronyms Used in this Document

Acronym	Description			
abus	analog local bus			
ADC	analog-to-digital converter			
AG	analog global			
AHB	AMBA (advanced microcontroller bus archi- tecture) high-performance bus, an ARM data transfer bus			
ALU	arithmetic logic unit			
AMUXBUS	analog multiplexer bus			
API	application programming interface			
APSR	application program status register			
ARM®	advanced RISC machine, a CPU architecture			
ATM	automatic thump mode			
BW	bandwidth			
CAN	Controller Area Network, a communications protocol			
CMRR	common-mode rejection ratio			
CPU	central processing unit			
CRC	cyclic redundancy check, an error-checking protocol			
DAC	digital-to-analog converter, see also IDAC, VDAC			
DFB	digital filter block			
DIO	digital input/output, GPIO with only digital capabilities, no analog. See GPIO.			
DMIPS	Dhrystone million instructions per second			
DMA	direct memory access, see also TD			
DNL	differential nonlinearity, see also INL			
DNU	do not use			
DR	port write data registers			
DSI	digital system interconnect			
DWT	data watchpoint and trace			
ECC	error correcting code			
ECO	external crystal oscillator			
EEPROM	electrically erasable programmable read-only memory			
EMI	electromagnetic interference			
EMIF	external memory interface			
EOC	end of conversion			
EOF	end of frame			
EPSR	execution program status register			
ESD	electrostatic discharge			

Acronym	Description				
ETM	embedded trace macrocell				
FIR	finite impulse response, see also IIR				
FPB	flash patch and breakpoint				
FS	full-speed				
GPIO	general-purpose input/output, applies to a PSoC pin				
HVI	high-voltage interrupt, see also LVI, LVD				
IC	integrated circuit				
IDAC	current DAC, see also DAC, VDAC				
IDE	integrated development environment				
I ² C, or IIC	Inter-Integrated Circuit, a communications protocol				
lir	infinite impulse response, see also FIR				
ILO	internal low-speed oscillator, see also IMO				
IMO	internal main oscillator, see also ILO				
INL	integral nonlinearity, see also DNL				
I/O	input/output, see also GPIO, DIO, SIO, USBIO				
IPOR	initial power-on reset				
IPSR	interrupt program status register				
IRQ	interrupt request				
ITM	instrumentation trace macrocell				
LCD	liquid crystal display				
LIN	Local Interconnect Network, a communications				
LR	link register				
LUT	lookup table				
LVD	low-voltage detect, see also LVI				
LVI	low-voltage interrupt, see also HVI				
LVTTL	low-voltage transistor-transistor logic				
MAC	multiply-accumulate				
MCU	microcontroller unit				
MISO	master-in slave-out				
NC	no connect				
NMI	nonmaskable interrupt				
NRZ	non-return-to-zero				
NVIC	nested vectored interrupt controller				
NVL	nonvolatile latch, see also WOL				
opamp	operational amplifier				
PAL	programmable array logic, see also PLD				
PC	program counter				
РСВ	printed circuit board				



Table 44. Acronyms Used in this Document (continued)

Acronym	Description		
PGA	programmable gain amplifier		
PHUB	peripheral hub		
PHY	physical layer		
PICU	port interrupt control unit		
PLA	programmable logic array		
PLD	programmable logic device, see also PAL		
PLL	phase-locked loop		
PMDD	package material declaration data sheet		
POR	power-on reset		
PRES	precise power-on reset		
PRS	pseudo random sequence		
PS	port read data register		
PSoC [®]	Programmable System-on-Chip™		
PSRR	power supply rejection ratio		
PWM	pulse-width modulator		
RAM	random-access memory		
RISC	reduced-instruction-set computing		
RMS	root-mean-square		
RTC	real-time clock		
RTL	register transfer language		
RTR	remote transmission request		
RX	receive		
SAR	successive approximation register		
SC/CT	switched capacitor/continuous time		
SCL	l ² C serial clock		
SDA	l ² C serial data		
S/H	sample and hold		
SINAD	signal to noise and distortion ratio		
SIO	special input/output, GPIO with advanced features. See GPIO.		
SOC	start of conversion		
SOF	start of frame		
SPI	Serial Peripheral Interface, a communications protocol		
SR	slew rate		
SRAM	static random access memory		
SRES	software reset		
SWD	serial wire debug, a test protocol		
SWV	single-wire viewer		
TD	transaction descriptor, see also DMA		

Table 44. Acronyms Used in this Document (continued)

Acronym Description THD total harmonic distortion TIA transimpedance amplifier TRM technical reference manual TTL transistor-transistor logic ТΧ transmit UART Universal Asynchronous Transmitter Receiver, a communications protocol UDB universal digital block USB Universal Serial Bus USBIO USB input/output, PSoC pins used to connect to a USB port VDAC voltage DAC, see also DAC, IDAC WDT watchdog timer WOL write once latch, see also NVL WRES watchdog timer reset **XRES** external reset I/O pin **XTAL** crystal



Document Conventions

Units of Measure

Table 45. Units of Measure

Symbol	Unit of Measure			
°C	degrees Celsius			
dB	decibel			
fF	femto farad			
Hz	hertz			
KB	1024 bytes			
kbps	kilobits per second			
Khr	kilohour			
kHz	kilohertz			
kΩ	kilo ohm			
Ksps	kilosamples per second			
LSB	least significant bit			
Mbps	megabits per second			
MHz	megahertz			
MΩ	mega-ohm			
Msps	megasamples per second			
μA	microampere			
μF	microfarad			
μH	microhenry			
μs	microsecond			
μV	microvolt			
μW	microwatt			
mA	milliampere			
ms	millisecond			
mV	millivolt			
nA	nanoampere			
ns	nanosecond			
nV	nanovolt			
Ω	ohm			
pF	picofarad			
ppm	parts per million			
ps	picosecond			
S	second			
sps	samples per second			
sqrtHz	square root of hertz			
V	volt			



Document History Page

Document Title: Automotive PSoC [®] 4: PSoC 4100 Family Datasheet Programmable System-on-Chip (PSoC [®]) Document Number: 001-93576				
Revision	ECN	Orig. of Change	Submission Date	Description of Change
*B	5071385	THOR / KIKU	01/21/2016	Changed status from Preliminary to Final.
*C	5117912	MVRE	01/31/2016	Updated Features: Updated Programmable Analog: Replaced "Two opamps" with "One opamp". Updated Block Diagram: Replaced "2x" with "1x". Updated Functional Overview: Updated Analog Blocks: Updated Opamp (CTBm Block): Replaced "Two opamps" with "Opamp" in heading. Updated description. Updated description. Updated Power: Updated Unregulated External Supply: Updated Table 1: Updated details in "Bypass Capacitors" column corresponding to "VDDD–VSS" and "VCCD–VSS" power supplies.
*D	5331416	MVRE	07/04/2016	Updated Functional Overview: Updated CPU and Memory Subsystem: Updated Flash: Updated description. Updated Fixed Function Digital: Updated Serial Communication Blocks (SCB): Updated description. Updated Pinouts: Updated Power: Added Figure 3. Updated Power: Added Figure 4. Updated Unregulated External Supply: Updated Table 1: Updated details in "Bypass Capacitors" column corresponding to "VDDD–VSS" and "VREF–VSS (optional)" Power Supply.



Document History Page (continued)

Revision	ECN	Orig. of Change	Submission Date	Description of Change
*D (cont.)	5331416	MVRE	07/04/2016	Updated Electrical Specifications:
				Updated Device-Level Specifications:
				Updated Table 3:
				Updated entire table.
				Updated Analog Peripherals:
				Updated Opamp:
				Updated Table 8:
				Updated values in "Typ" and "Max" columns for I _{DD_HI} , I _{DD_MED} , I _{DD_LOW} parameters.
				Updated details in "Details/Conditions" column corresponding to "SID290"
				Spec ID and "V _{OS_DR_TR} " parameter. Added SID290Q Spec ID corresponding to V _{OS_DR_TR} parameter and its
				details.
				Added SID299A Spec ID corresponding to OL_GAIN parameter and its details
				Updated Comparator:
				Updated Table 9:
				Updated details in "Description", "Min", "Typ", "Max" columns corresponding to
				"I _{CMP1} ", "I _{CMP2} " and "I _{CMP3} " parameters. Updated Table 10:
				Updated details in "Description", "Min", "Typ", "Max" columns corresponding to
				"T _{RESP1} ", "T _{RESP2} " and "T _{RESP3} " parameters. Updated Digital Peripherals:
				Removed "Timer".
				Removed "Counter".
				Removed "Pulse Width Modulation (PWM)".
				Added Timer/Counter/PWM.
				Updated I ² C:
				Updated Table 16:
				Changed maximum value of I _{I2C1} parameter from 10.5 µA to 50 µA.
				Updated LCD Direct Drive:
				Updated Table 20:
				Changed maximum value of I_{UART1} parameter from 9 µA to 55 µA.
				Updated SPI Specifications:
				Updated Table 25:
				Replaced "FCPU" with "Tscbclk" in "Max" column corresponding to T _{DSO}
				parameter.
				Updated Memory:
				Updated Table 27:
				Added F _{RETO} parameter and its details.



Document History Page (continued)

Document Title: Automotive PSoC [®] 4: PSoC 4100 Family Datasheet Programmable System-on-Chip (PSoC [®]) Document Number: 001-93576				
Revision	ECN	Orig. of Change	Submission Date	Description of Change
*D (cont.)	5331416	MVRE	07/04/2016	Updated Electrical Specifications: Updated System Resources: Updated Power-on-Reset (POR) with Brown Out: Updated Table 29: Updated details in "Details/Conditions" column corresponding to V _{FALLPPOR} parameter. Added Svdd parameter and its details. Updated Internal Main Oscillator: Updated Table 34: Updated details in "Details/Conditions" column corresponding to F _{IMOTOL1} parameter. Updated Internal Low-Speed Oscillator: Updated Table 36: Updated details in "Details/Conditions" column corresponding to F _{ILOTRIM1} parameter. Updated description. Updated description. Updated to new template. Completing Sunset Review.
*E	5675099	SNPR	03/28/2017	Updated Ordering Information: Updated part numbers. Updated to new template.
*F	5751084	SNPR	05/26/2017	No technical updates. Completing Sunset Review.



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Document Number: 001-93576 Rev. *F

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